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George et al.

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(54) **METHOD FOR THERMAL-SLIDE
DEBONDING OF TEMPORARY BONDED
SEMICONDUCTOR WAFERS**

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Related U.S. Application Data

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(51) **Int. Cl.**
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H01L 21/683 (2006.01)
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(52) **U.S. Cl.**
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Y10T 156/1911; Y10T 156/1944; Y10T
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H01L 21/67748; H01L 21/67751; H01L
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USPC 156/707, 711, 718, 752, 758, 763
See application file for complete search history.

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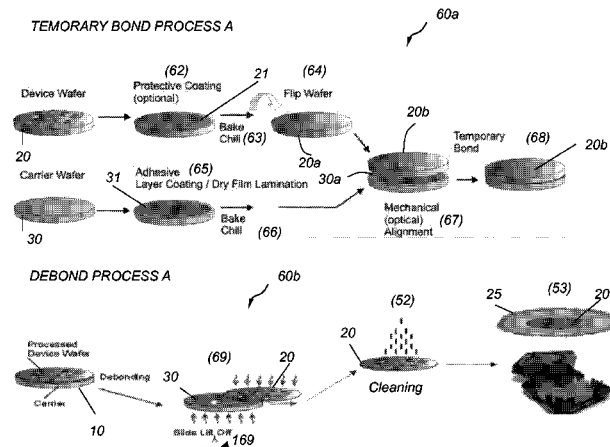
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(57)

ABSTRACT

A method for debonding two temporary bonded wafers, includes providing a debonder comprising a top chuck assembly, a bottom chuck assembly, a static gantry supporting the top chuck assembly, an X-axis carriage drive supporting the bottom chuck assembly and an X-axis drive control configured to drive horizontally the X-axis carriage drive and the bottom chuck assembly from a loading zone to a process zone under the top chuck assembly and from the process zone back to the loading zone. Next, loading a wafer pair comprising a carrier wafer bonded to a device wafer via an adhesive layer upon the bottom chuck assembly at the loading zone oriented so that the unbonded surface of the device wafer is in contact with the bottom assembly. Next, driving the X-axis carriage drive and the bottom chuck assembly to the process zone under the top chuck assembly. Next, placing the unbonded surface of the carrier wafer in contact with the top chuck assembly and holding the carrier wafer by the top chuck assembly. Next, initiating horizontal motion of the X-axis carriage drive while heat is applied to the carrier wafer and while the carrier wafer is held by the top chuck assembly.

16 Claims, 40 Drawing Sheets



- (51) **Int. Cl.**
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(2013.01); **Y10S 156/93** (2013.01); **Y10S**
156/932 (2013.01); **Y10S 156/941** (2013.01);
Y10S 156/942 (2013.01); **Y10S 156/943**
(2013.01); **Y10T 29/49817** (2015.01); **Y10T**
29/53274 (2015.01); **Y10T 156/1132** (2015.01);
Y10T 156/1153 (2015.01); **Y10T 156/1158**
(2015.01); **Y10T 156/1168** (2015.01); **Y10T**
156/1189 (2015.01); **Y10T 156/1911** (2015.01);
Y10T 156/1917 (2015.01); **Y10T 156/1944**
(2015.01); **Y10T 156/1972** (2015.01); **Y10T**
156/1978 (2015.01); **Y10T 279/18** (2015.01);
Y10T 279/21 (2015.01); **Y10T 279/26**
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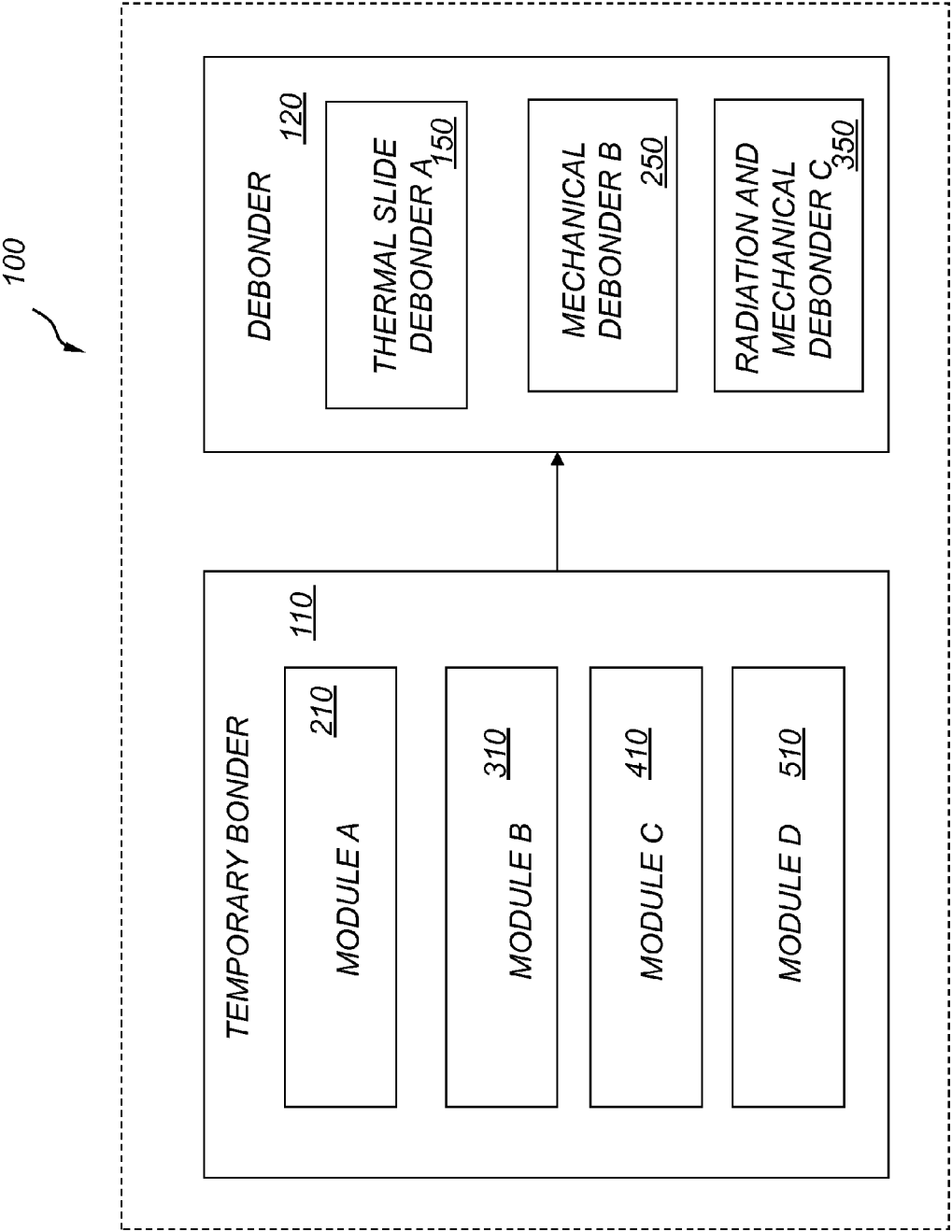
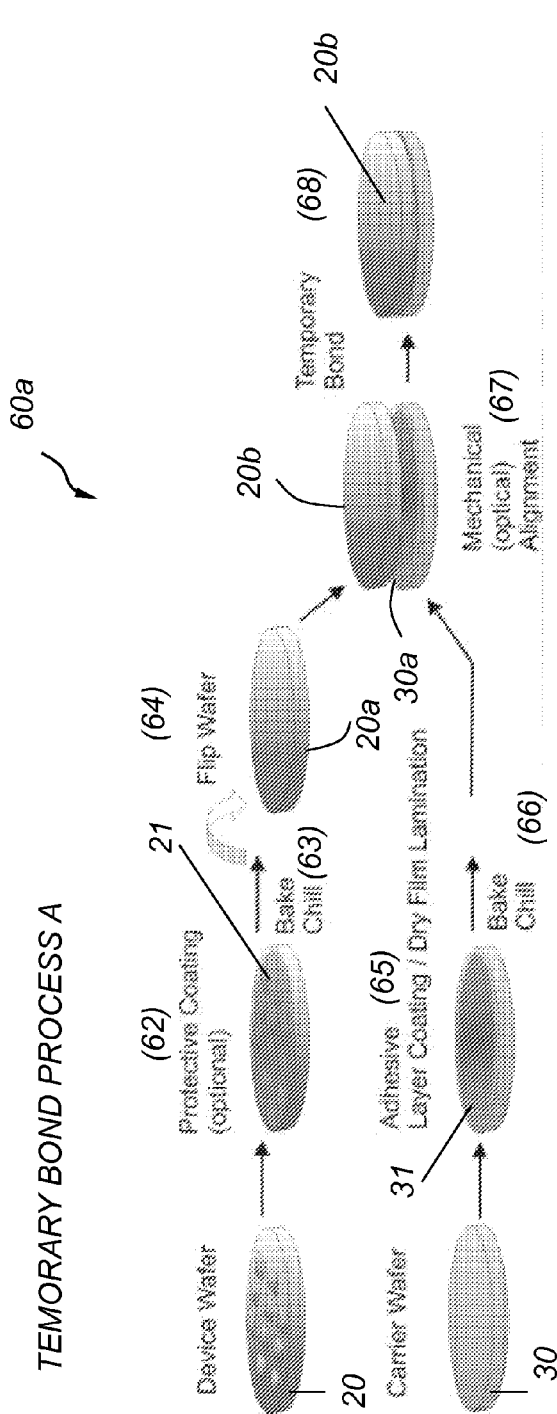


FIG. 1

TEMPORARY BOND PROCESS A



DEBOND PROCESS A

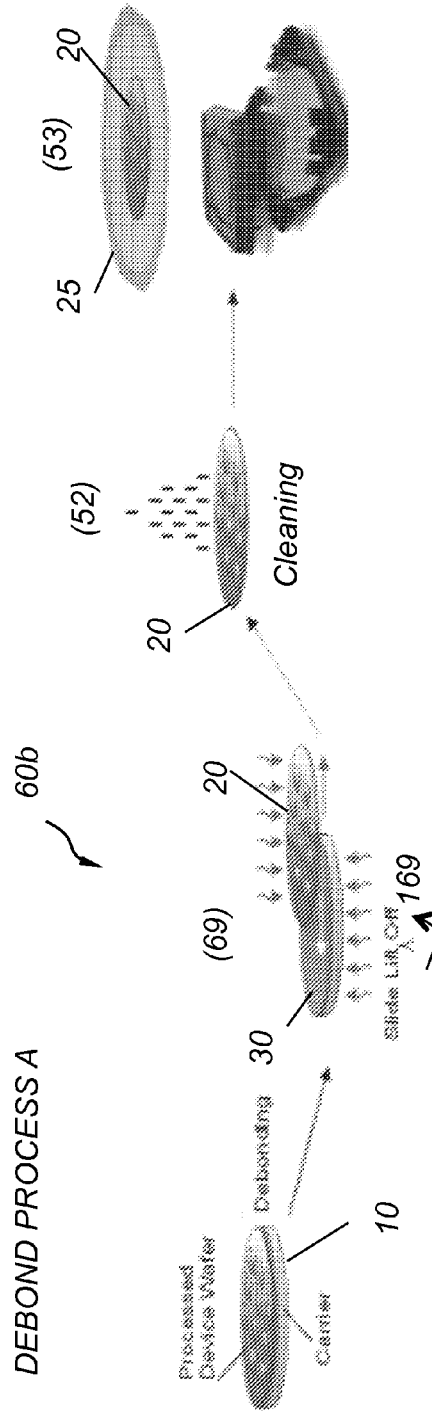
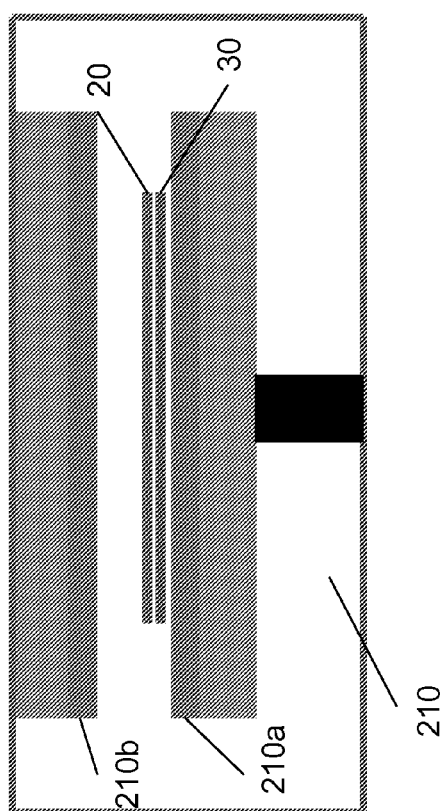


FIG. 1A



Process Basics

- Place bottom wafer on fixture chuck
- Place top adhesive carrier direct
- Manual Align
- Load into chamber
- Top chuck down, force
- Vacuum pump down
- Heat to ~200C
- Cool to unload temp
- Unload fixture

FIG. 1B

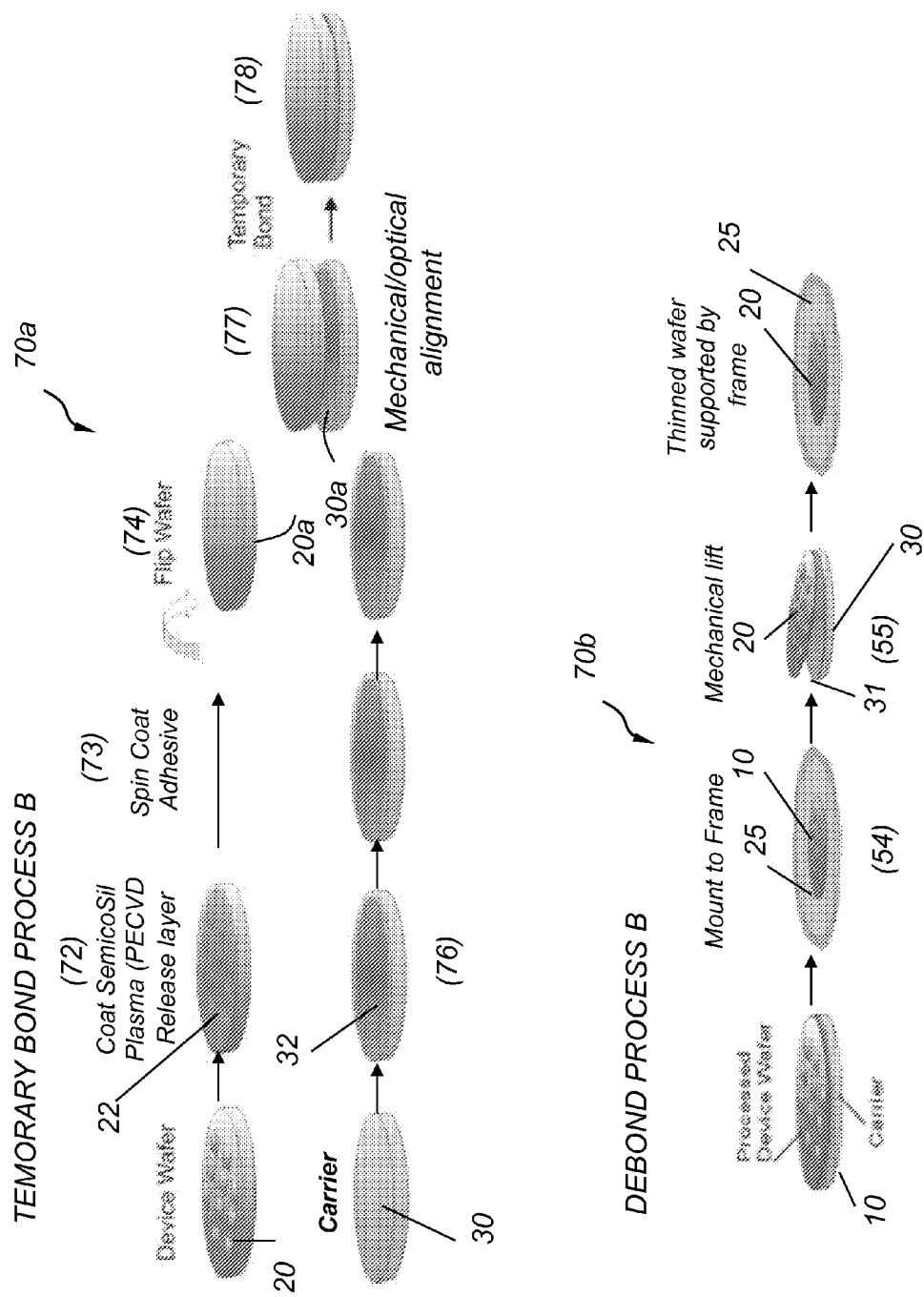
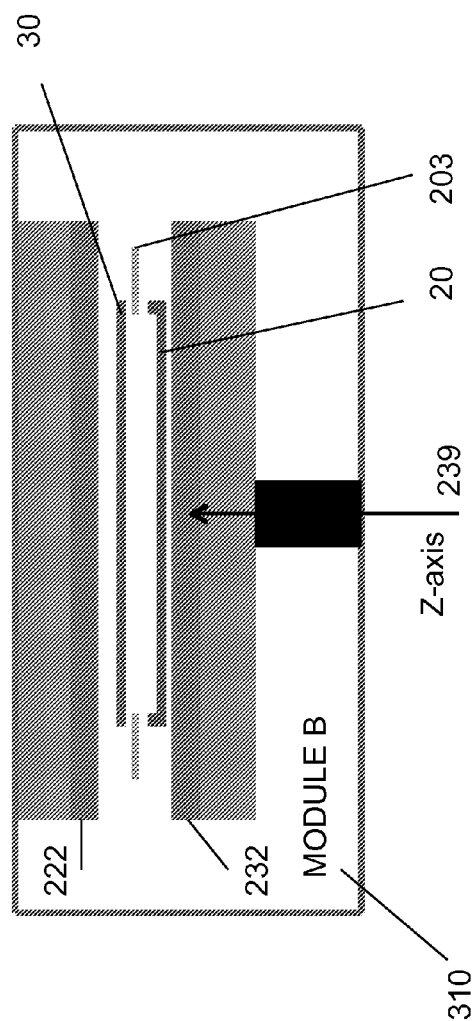


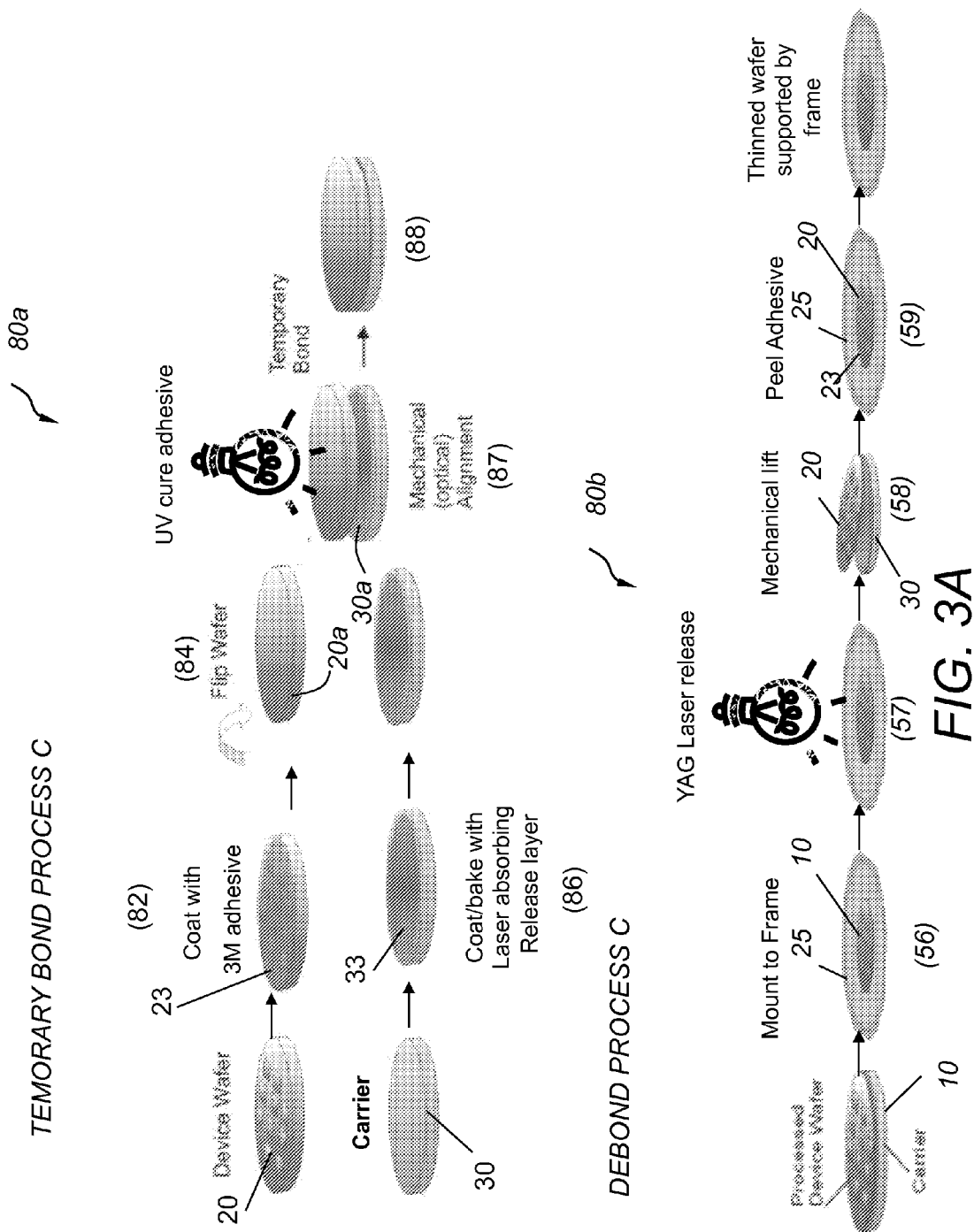
FIG. 2A



Process Basics

- Place bottom adhesive carrier on fixture
- Place top wafer on spacer flags
- Manual Align
- Load into chamber
- Vacuum pump down
- Remove spacers, drop wafer to edge bead
- Purge chamber (force)
- Heat to ~200C
- Cool to unload temp
- Unload fixture

FIG. 2B



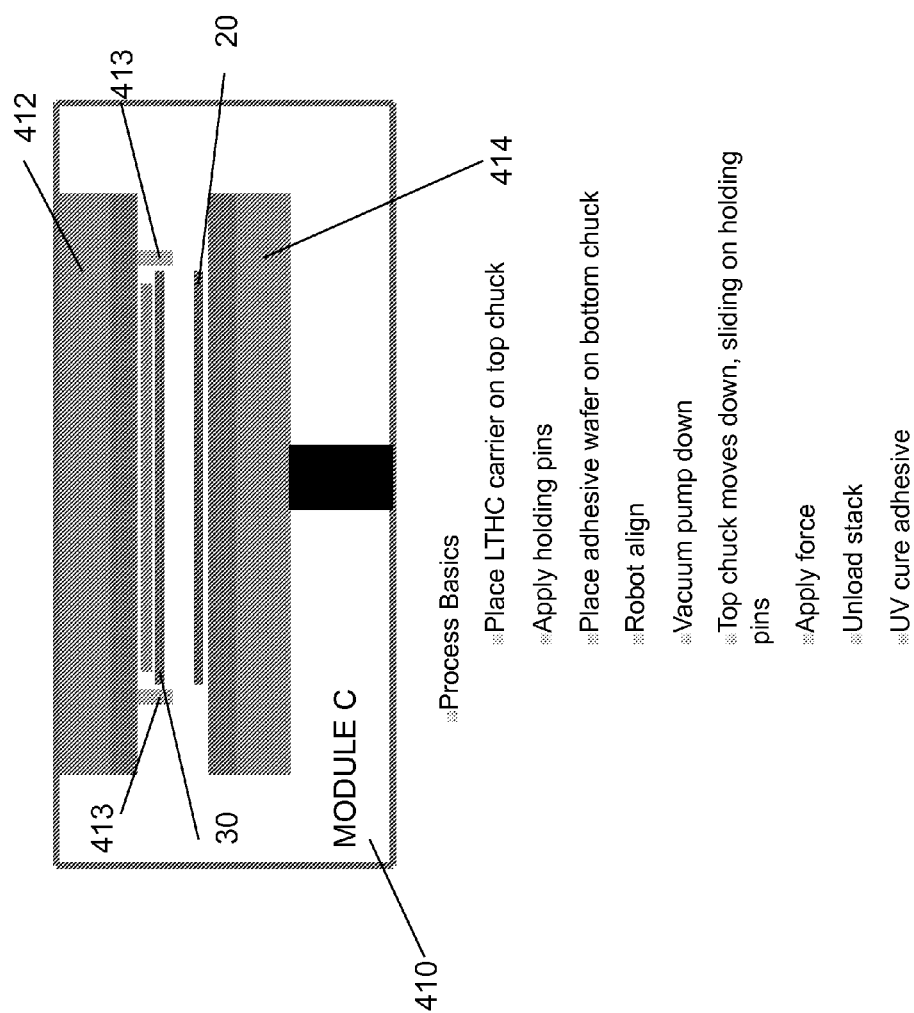


FIG. 3B

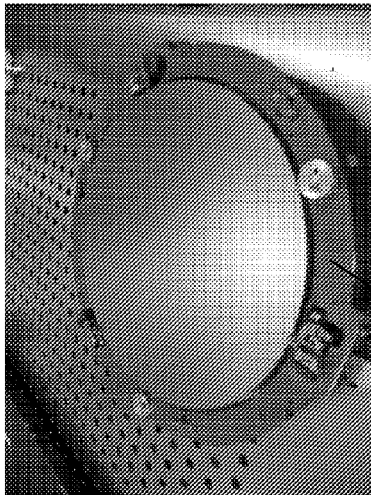


FIG. 4

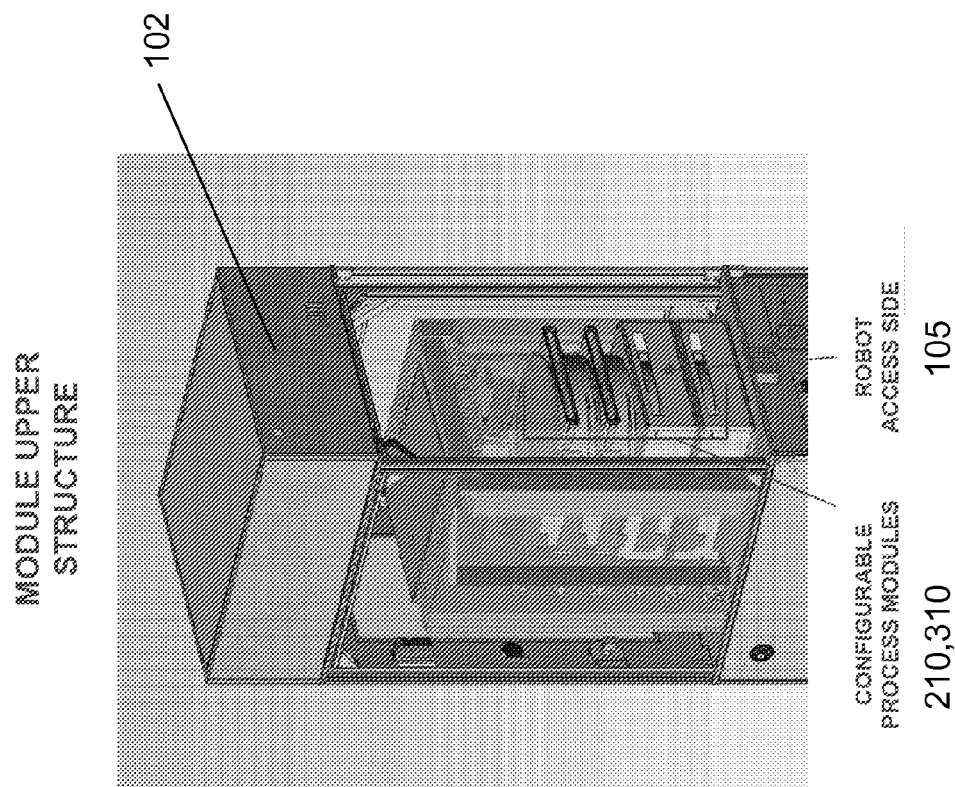


FIG. 5

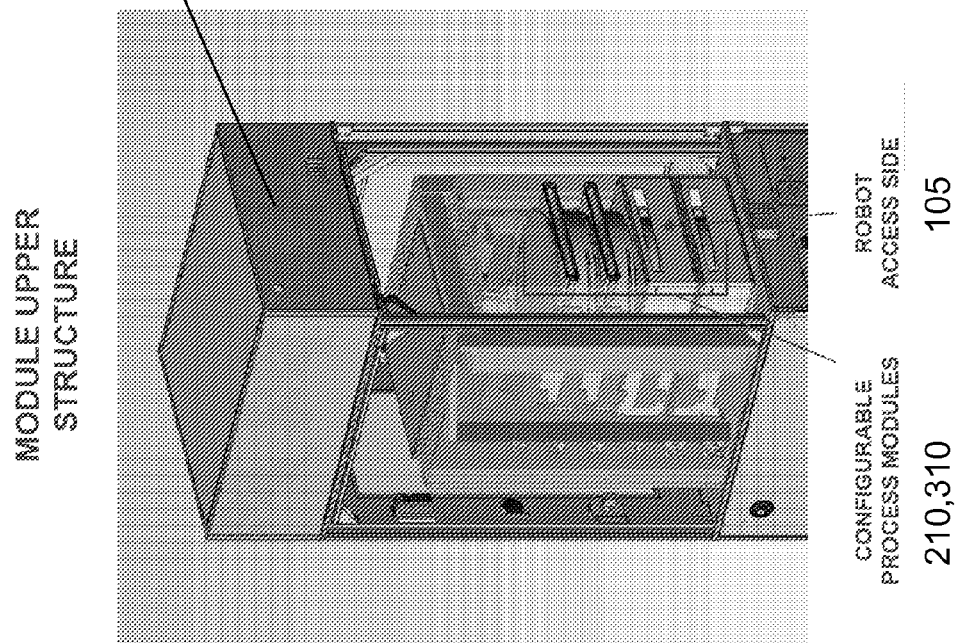


FIG. 6

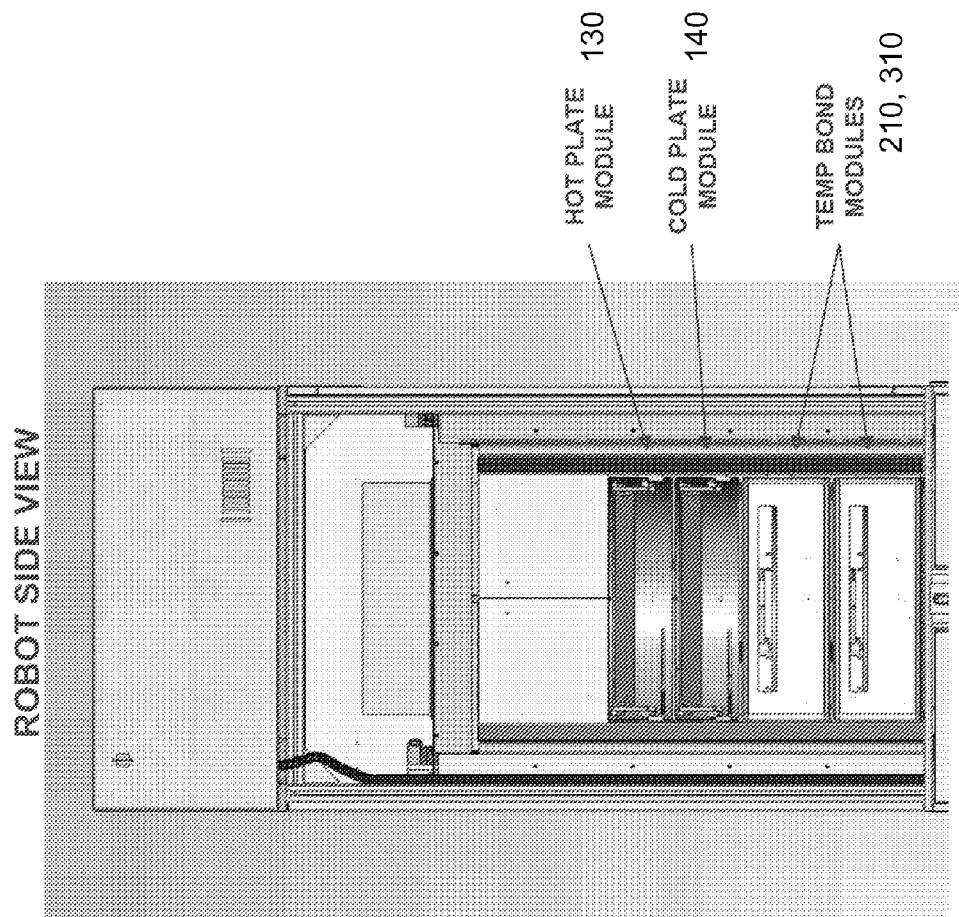


FIG. 7

HOT PLATE MODULE

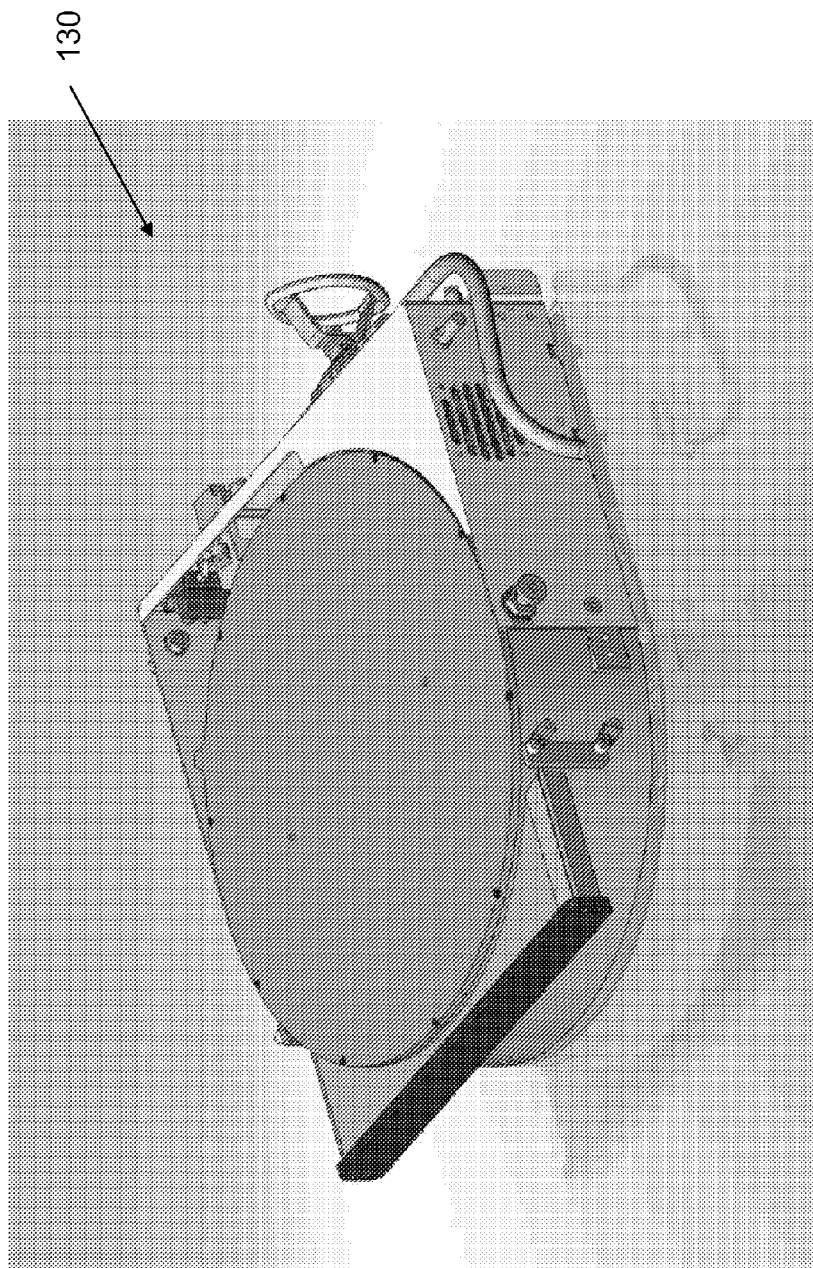


FIG. 8

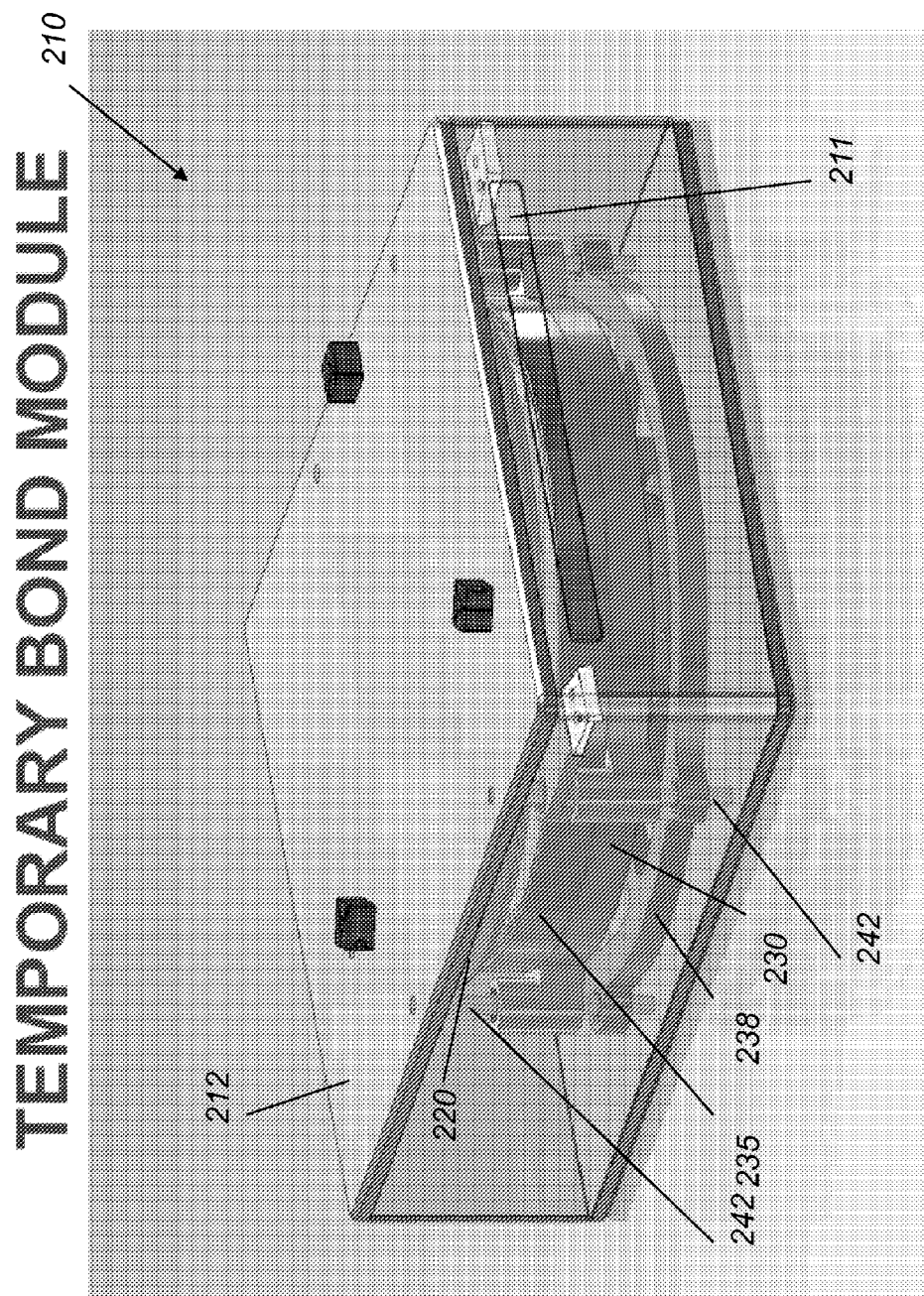


FIG. 9

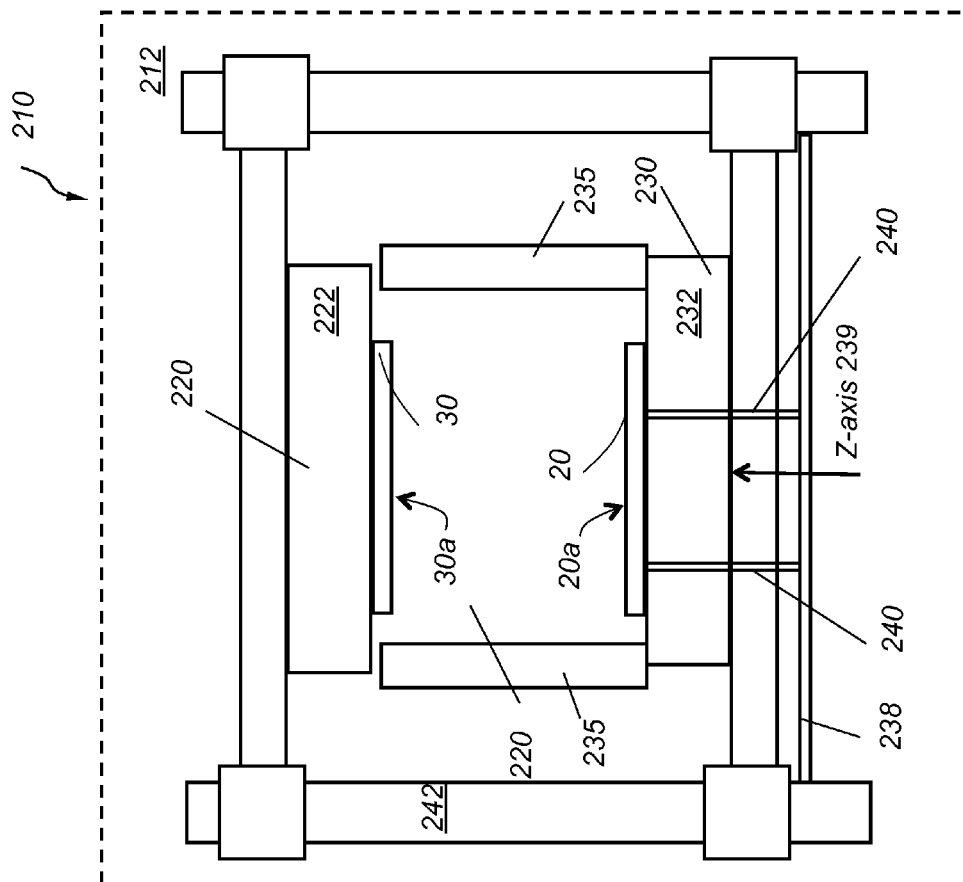


FIG. 10

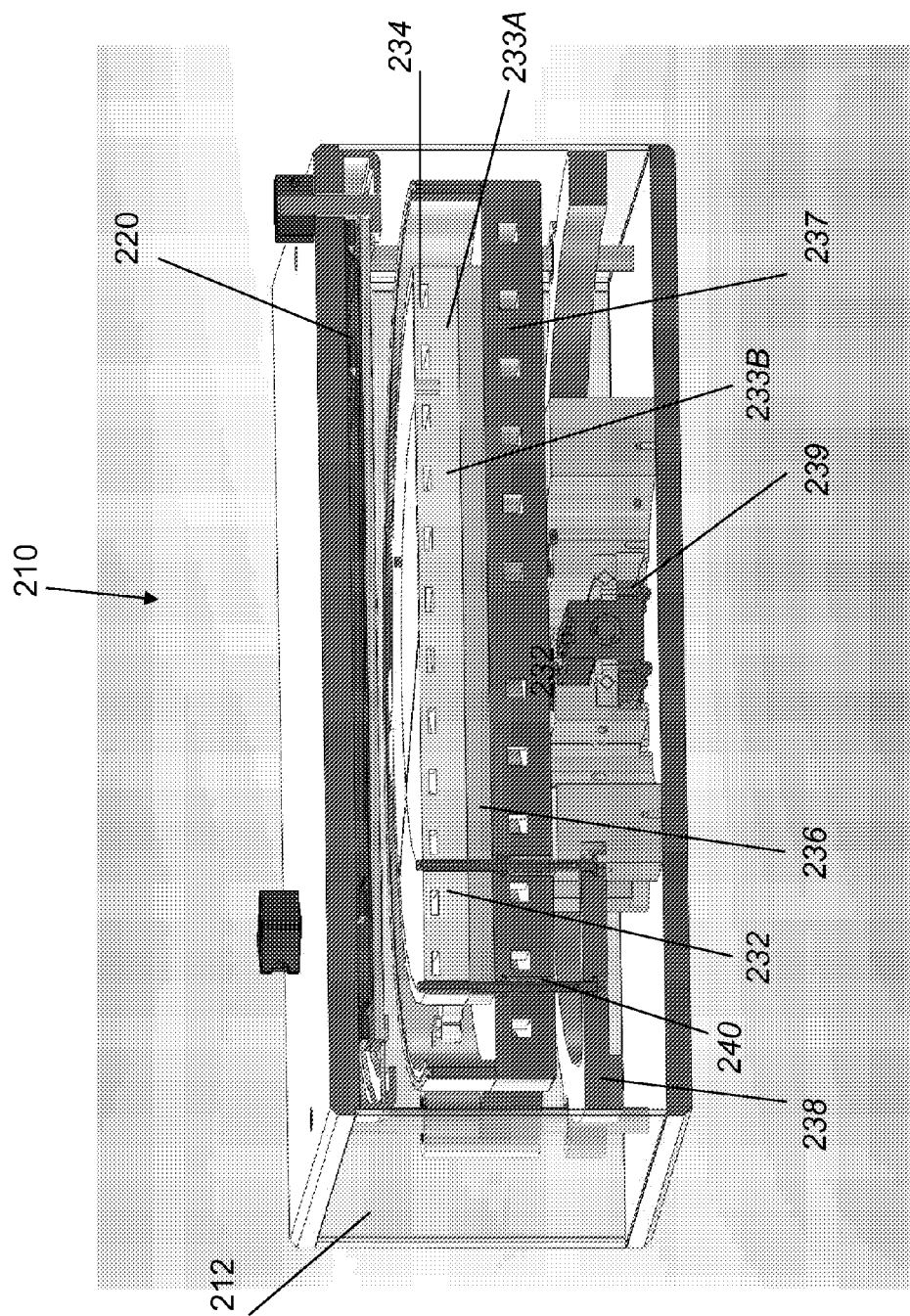


FIG. 11

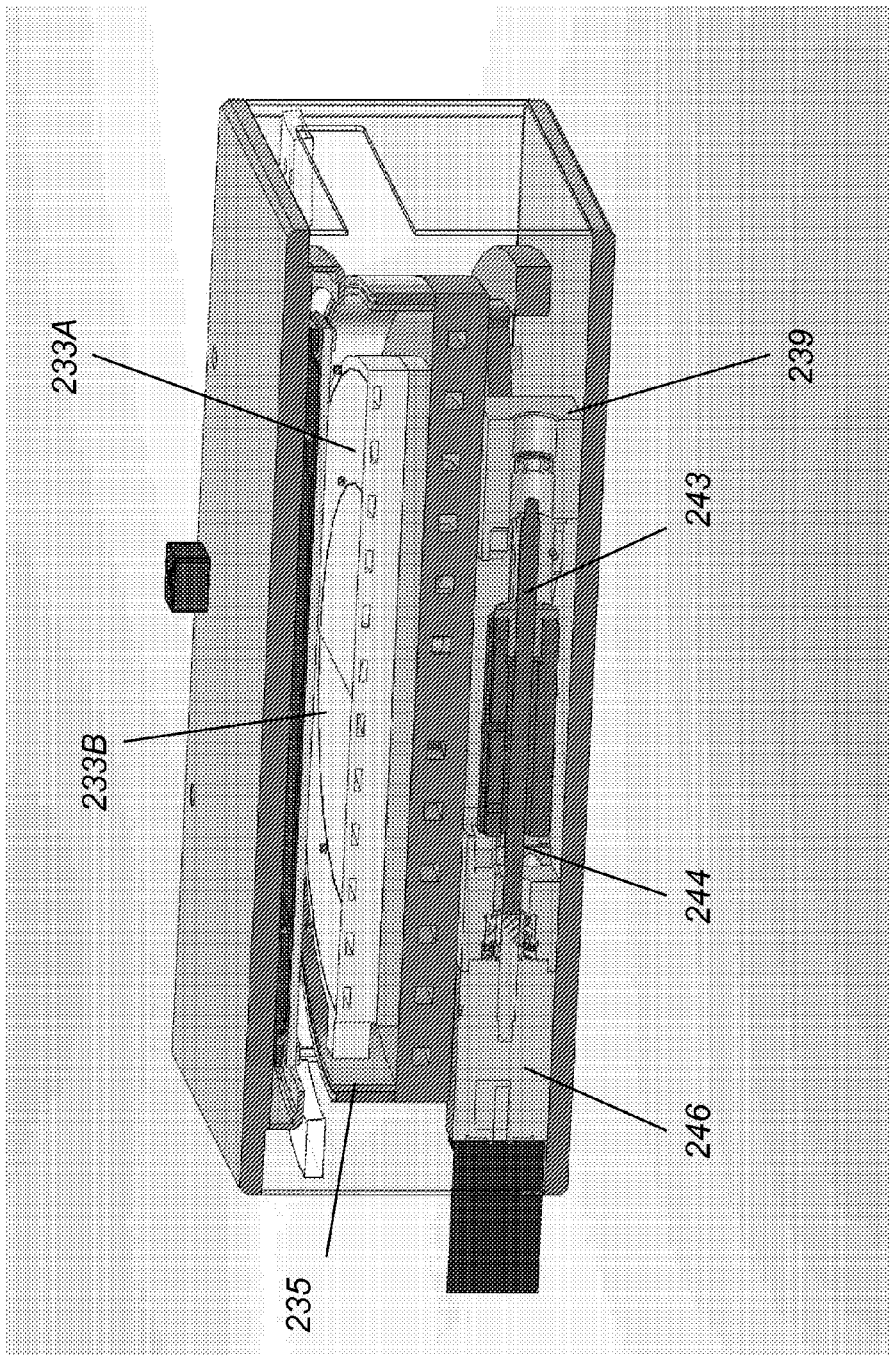


FIG. 12

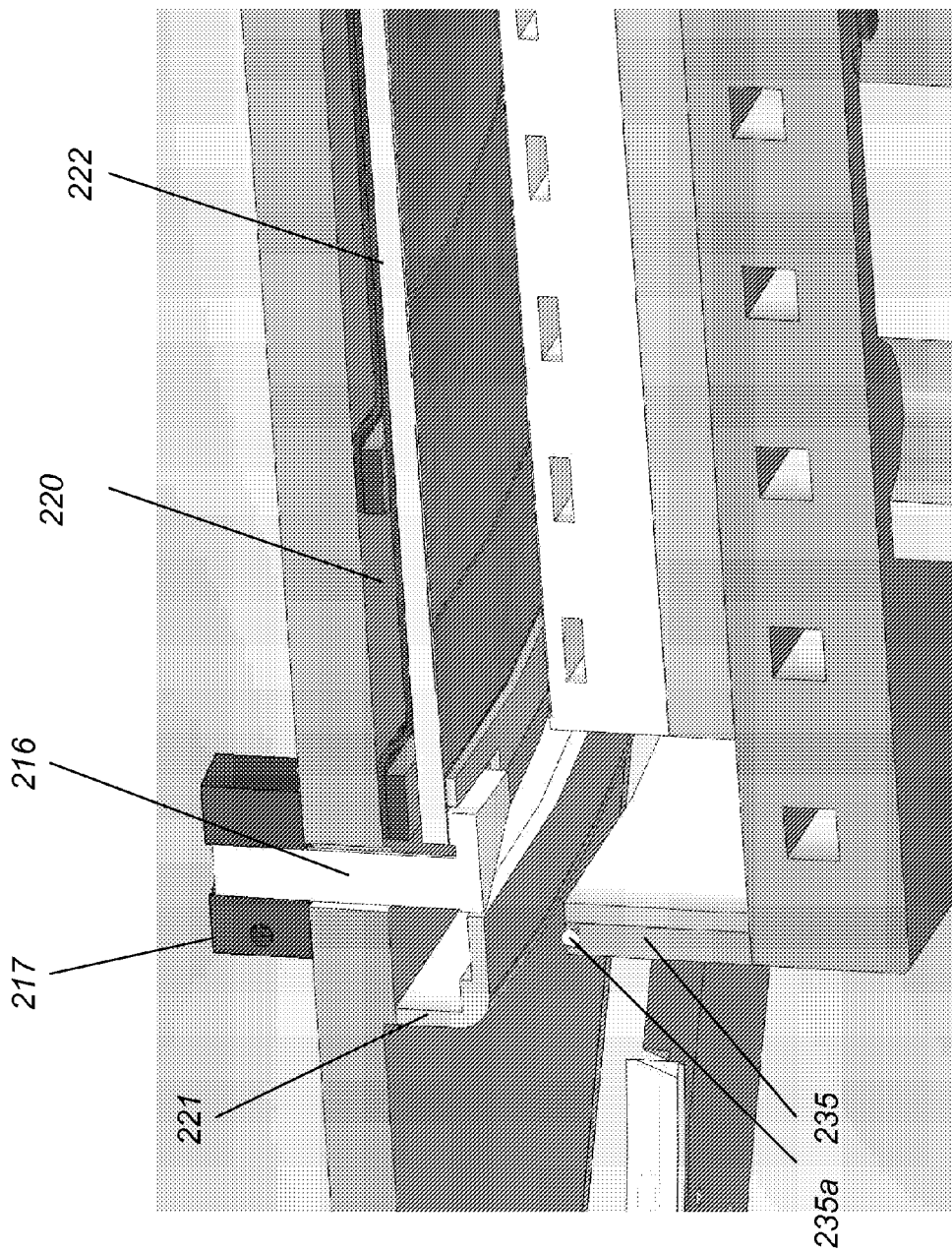
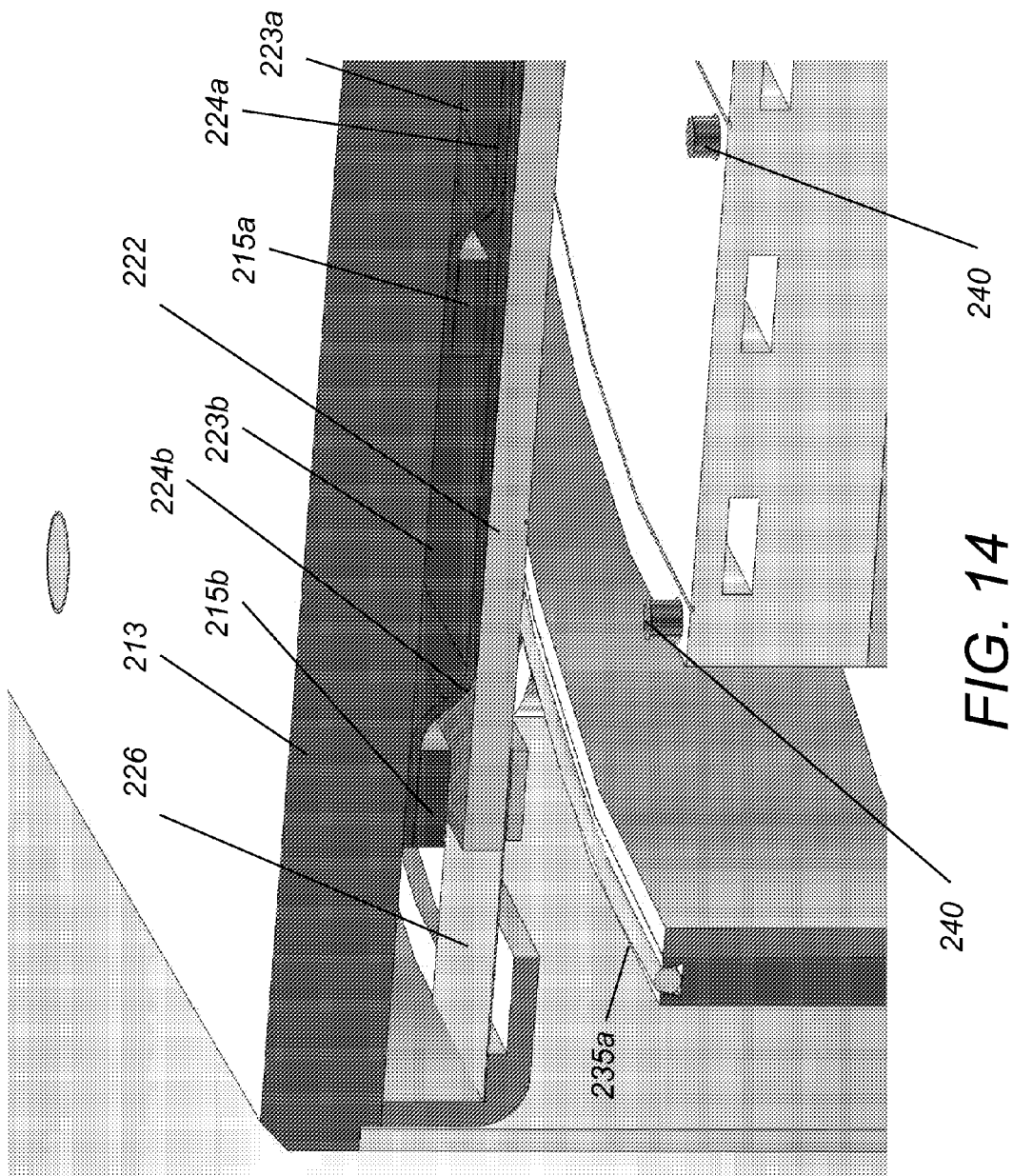


FIG. 13



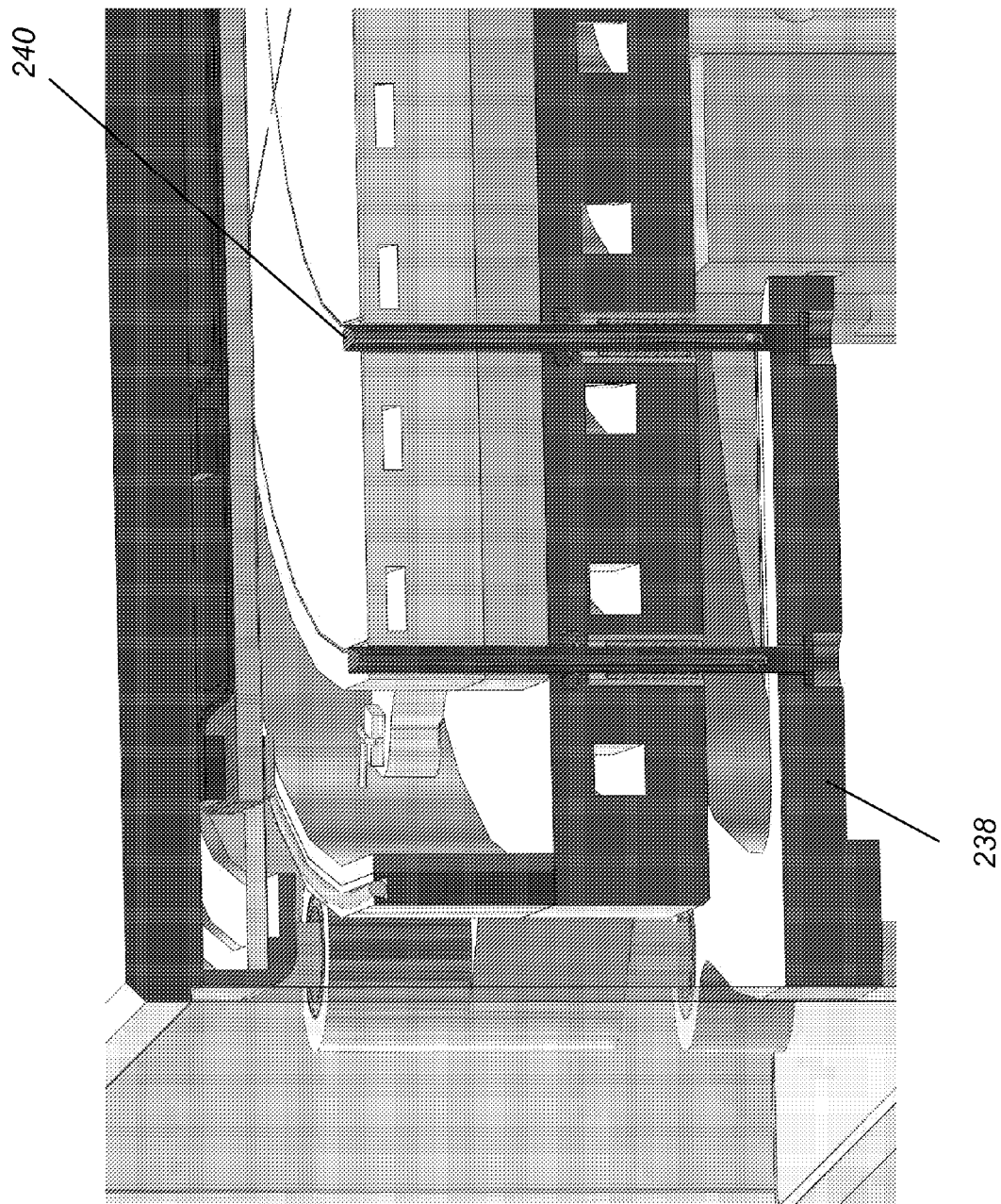


FIG. 15

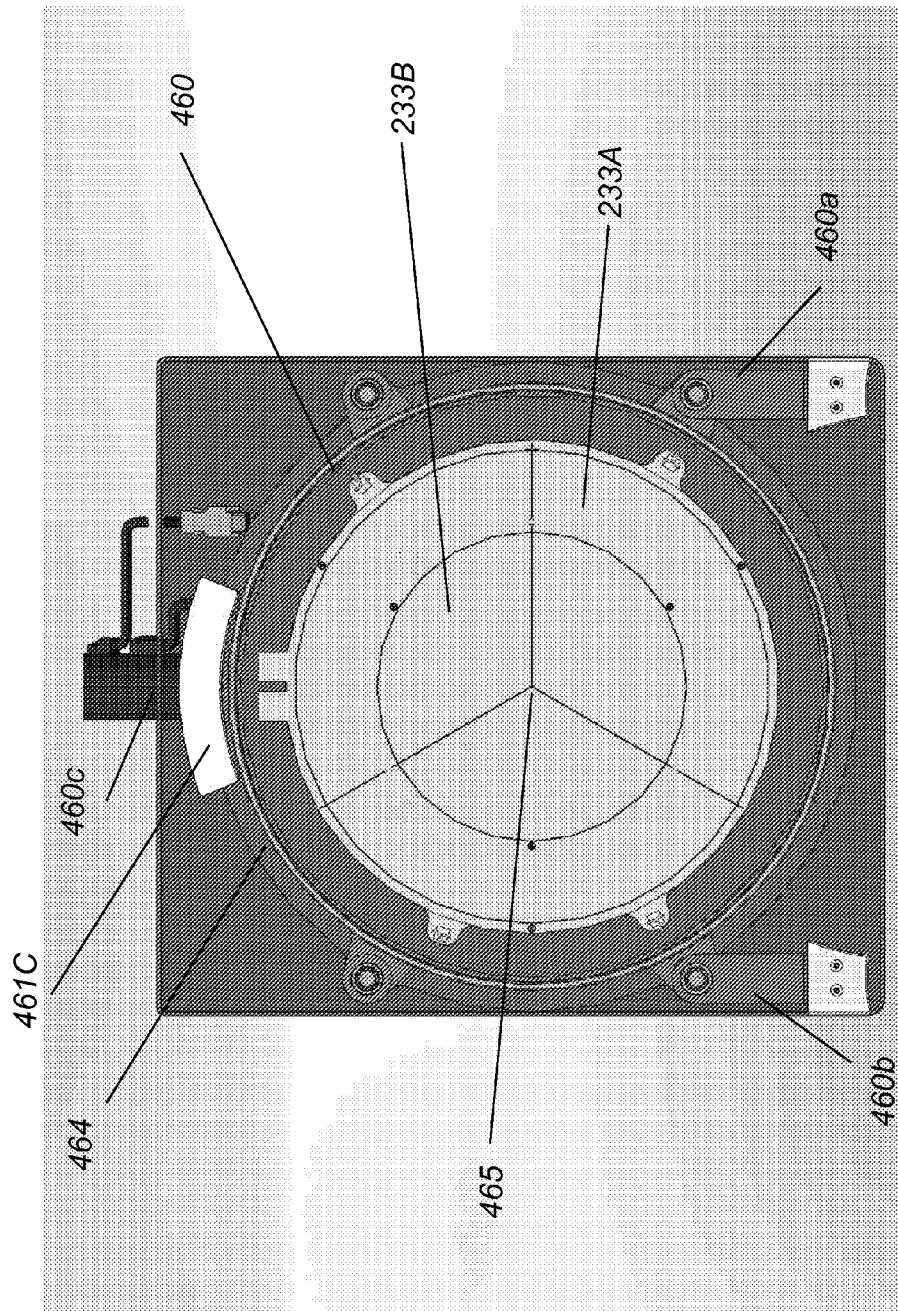
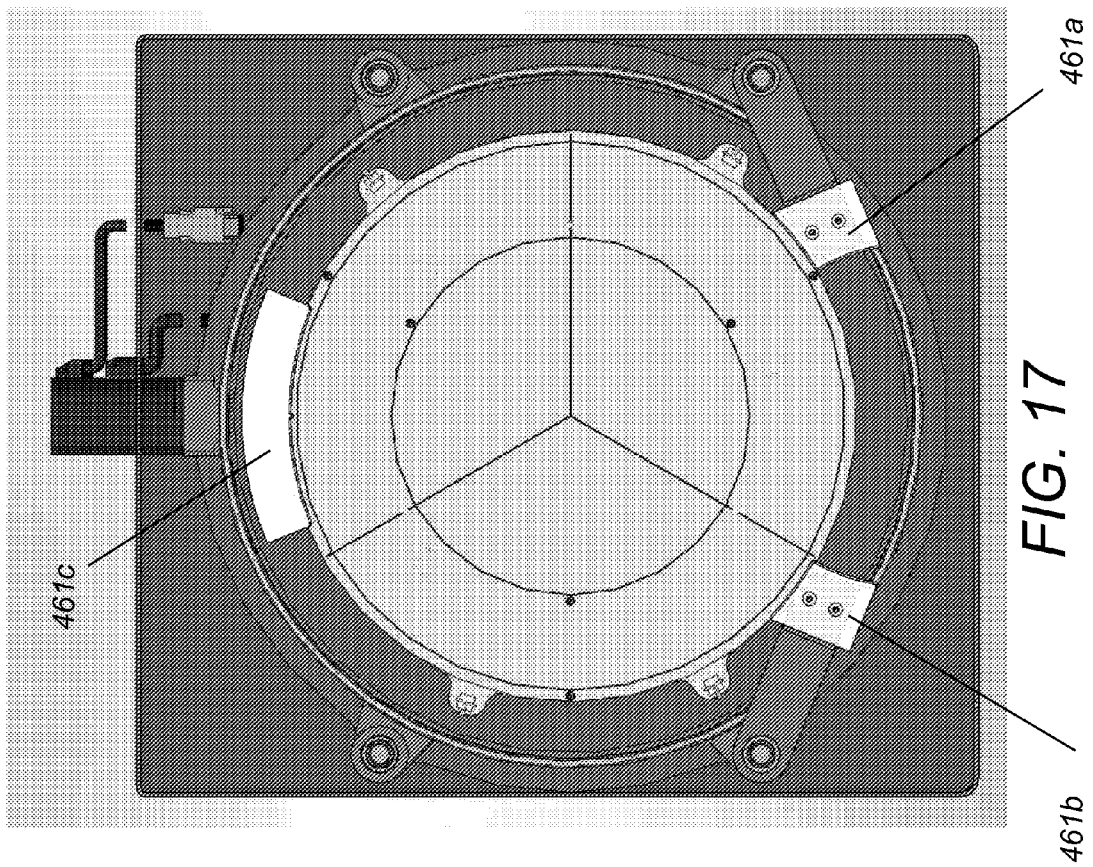


FIG. 16



300MM PREALIGNMENT

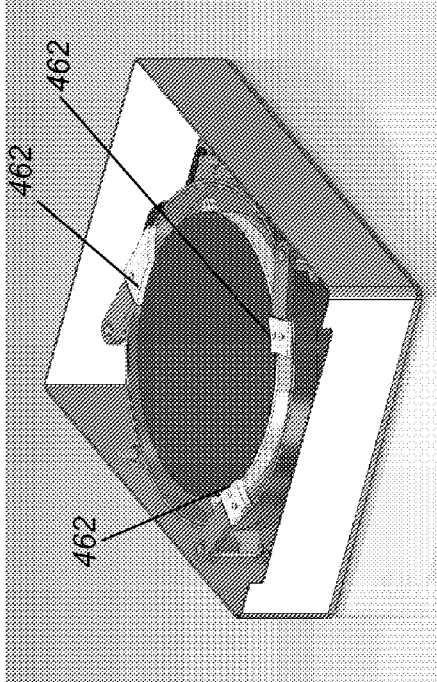


FIG. 18A

200MM PREALIGNMENT

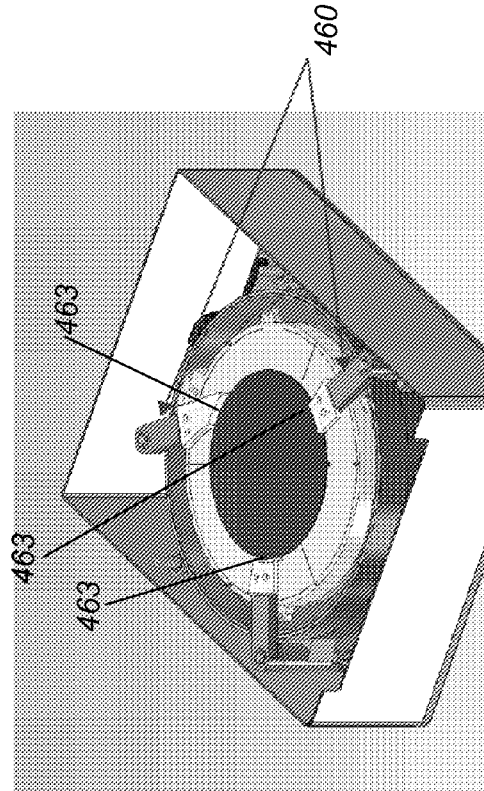
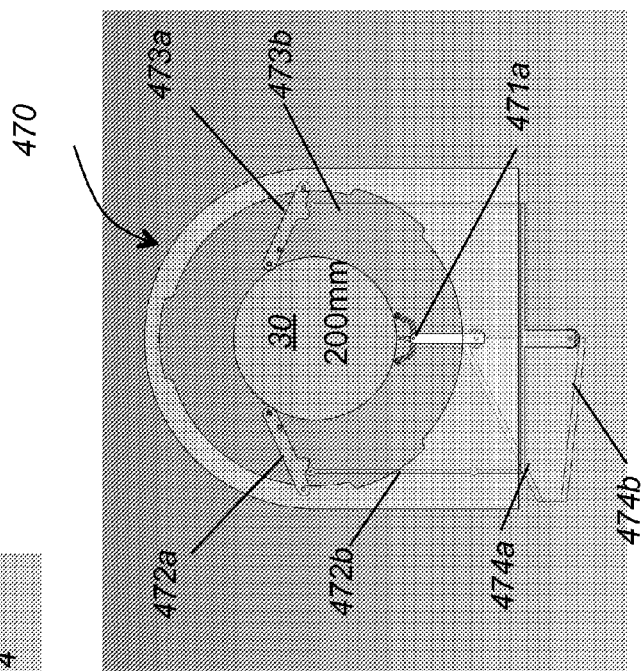
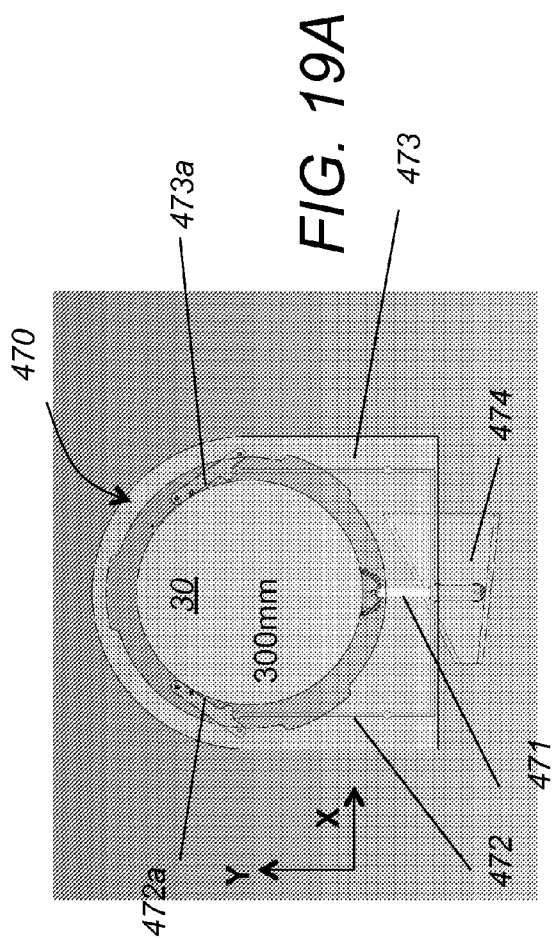


FIG. 18B



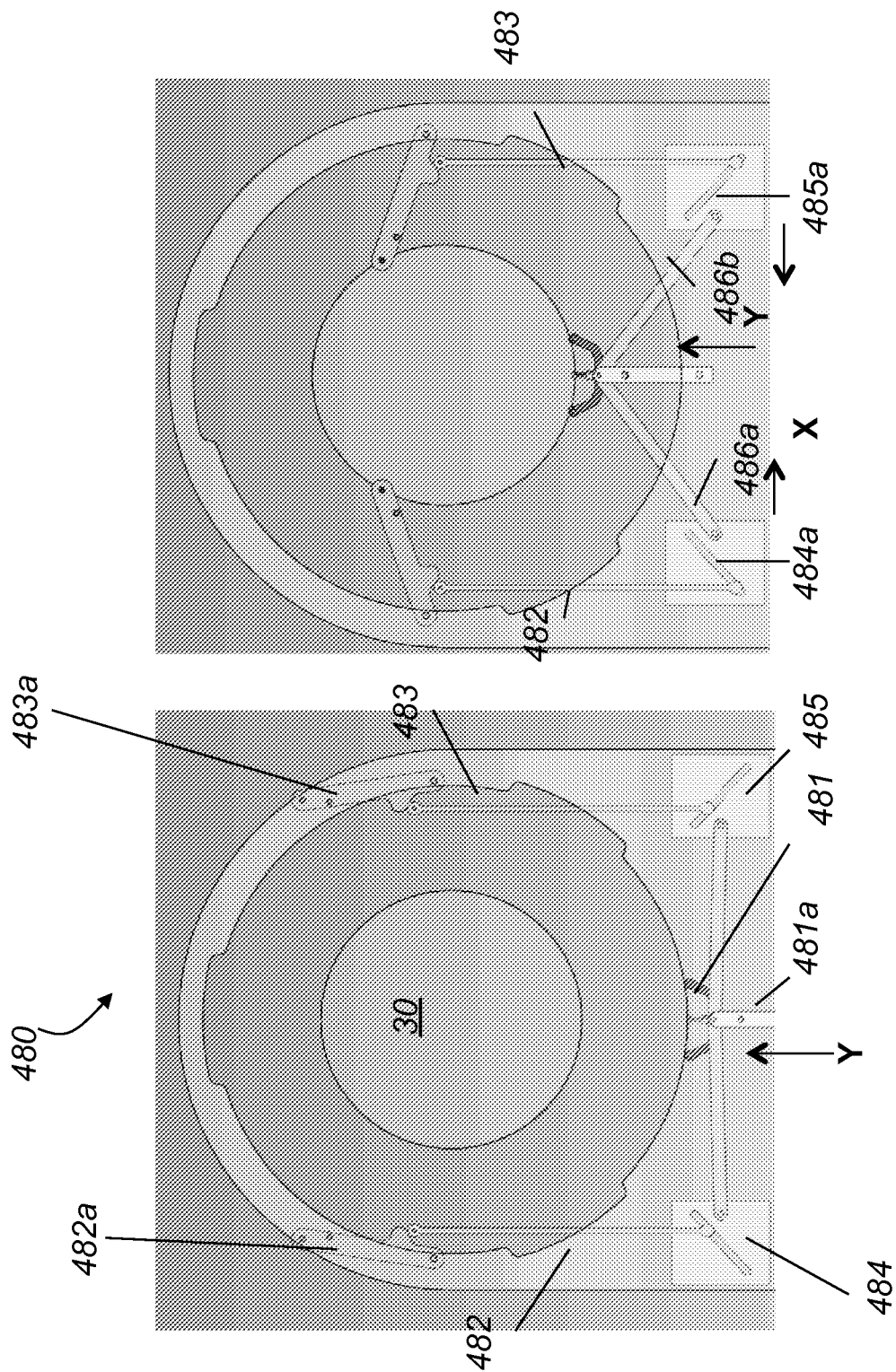


FIG. 19D

FIG. 19C

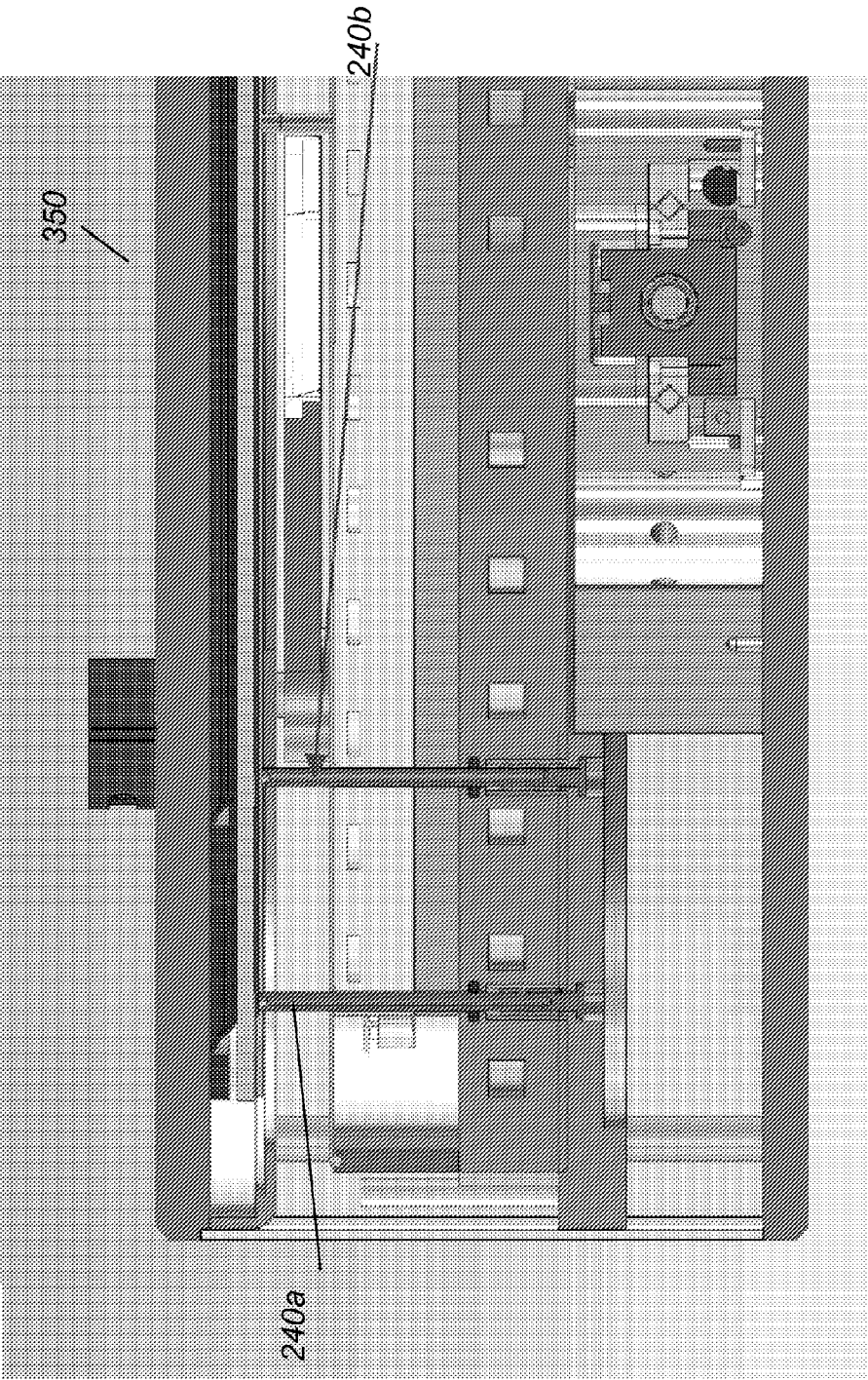


FIG. 20A

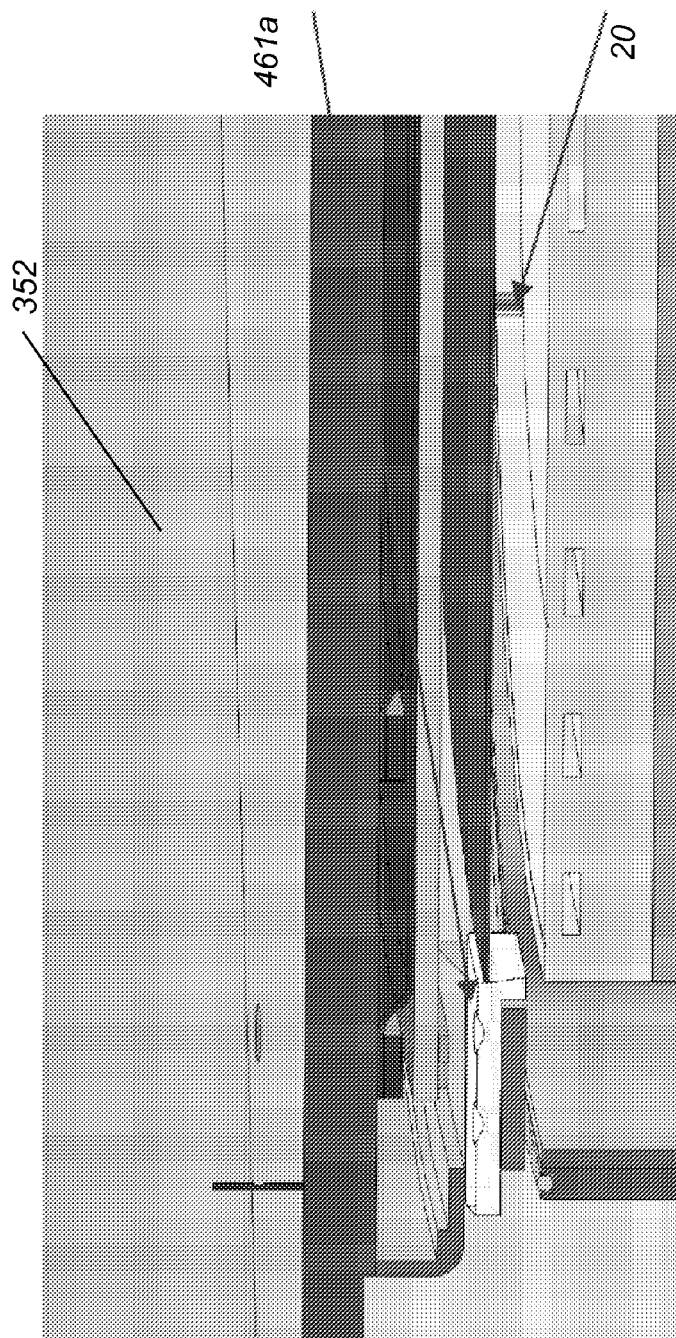


FIG. 20B

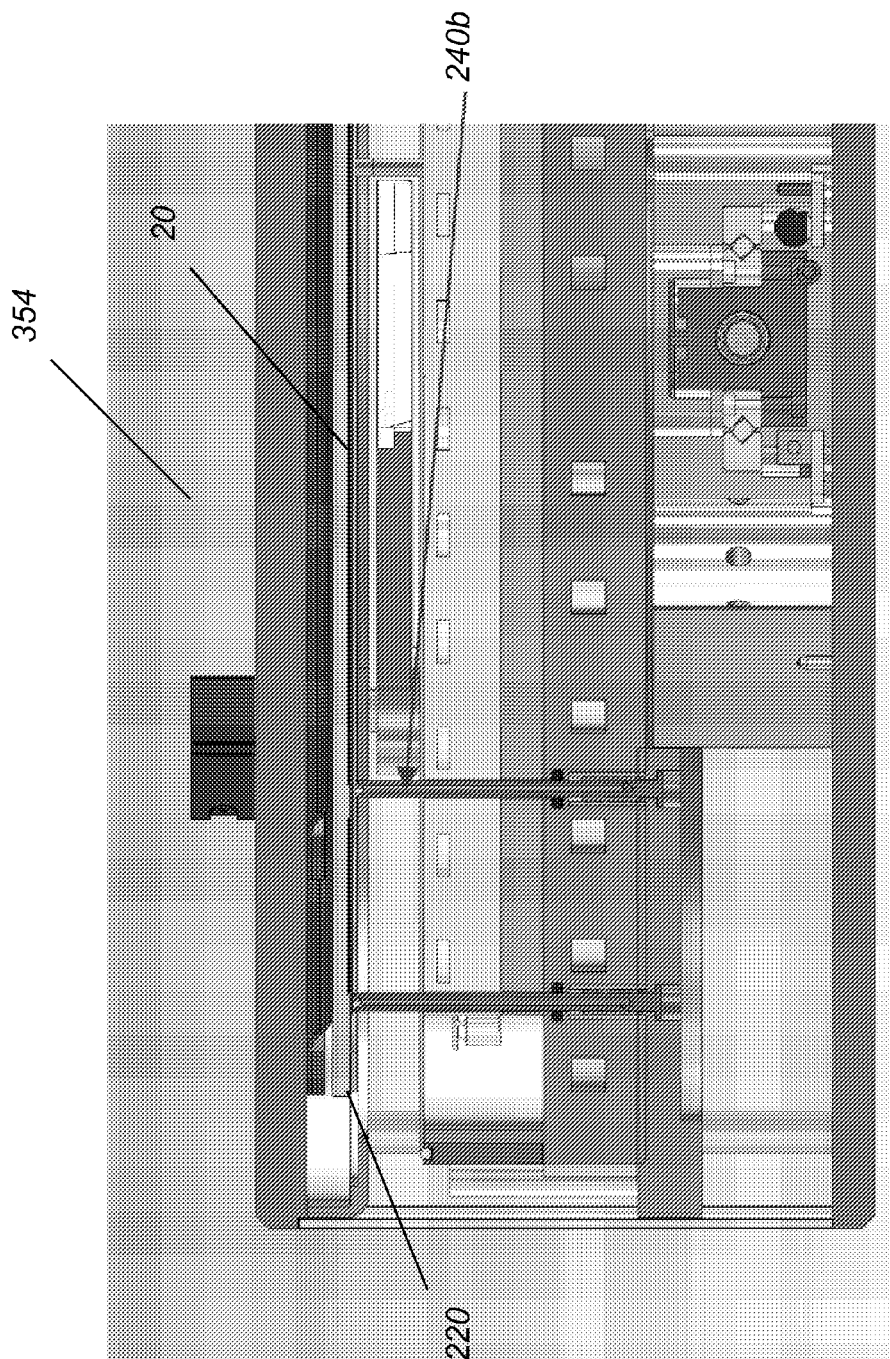


FIG. 20C

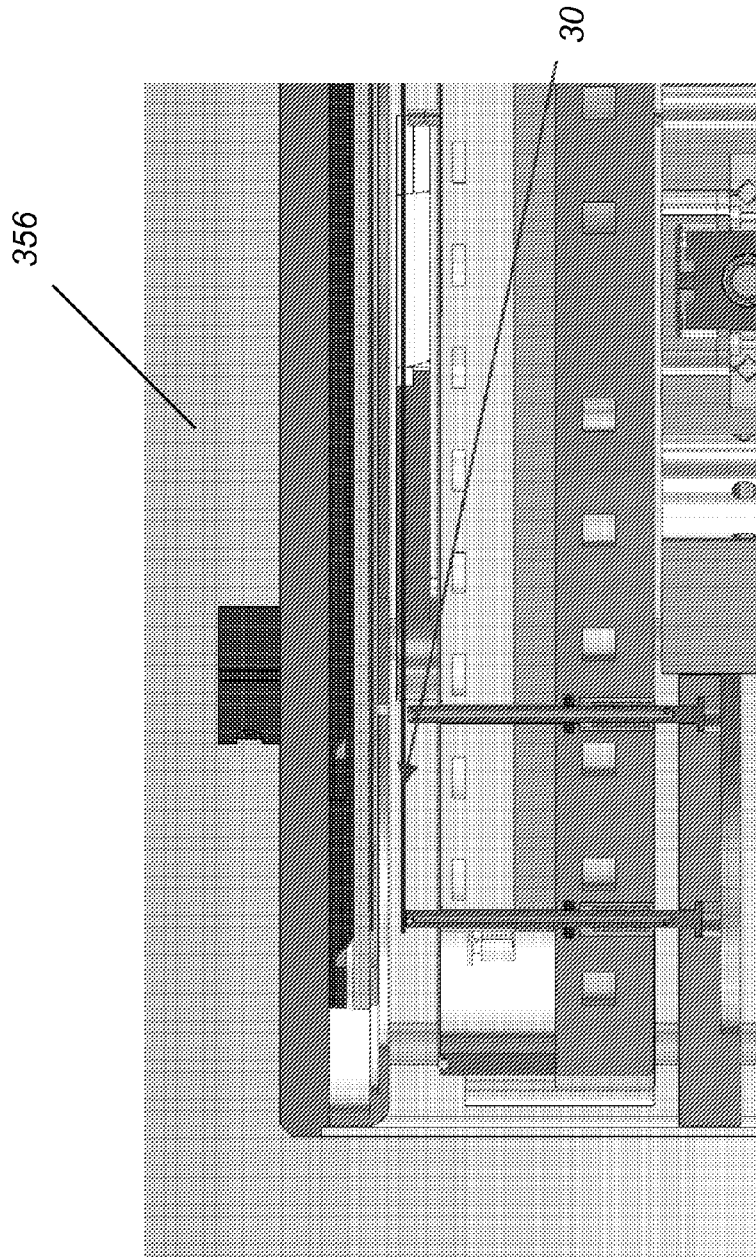


FIG. 21A

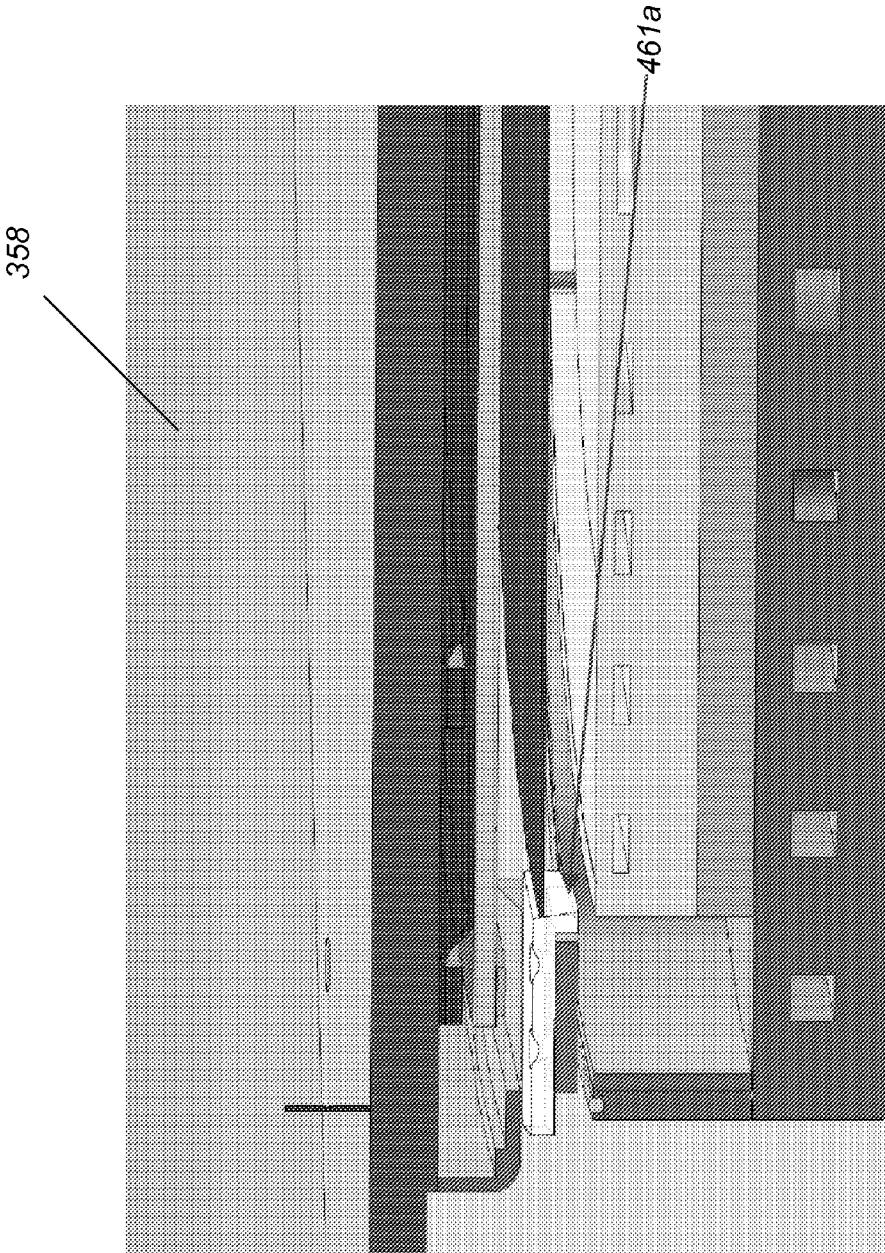


FIG. 21B

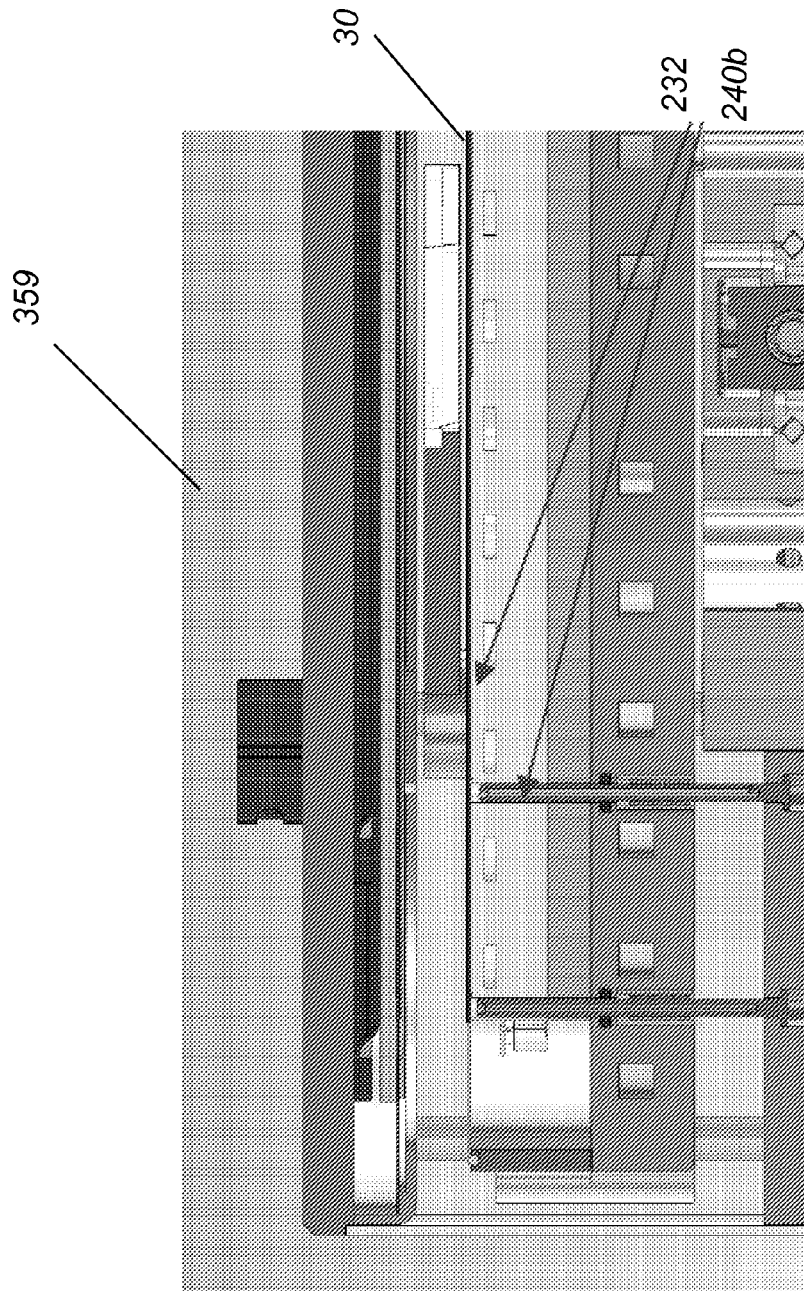


FIG. 21C

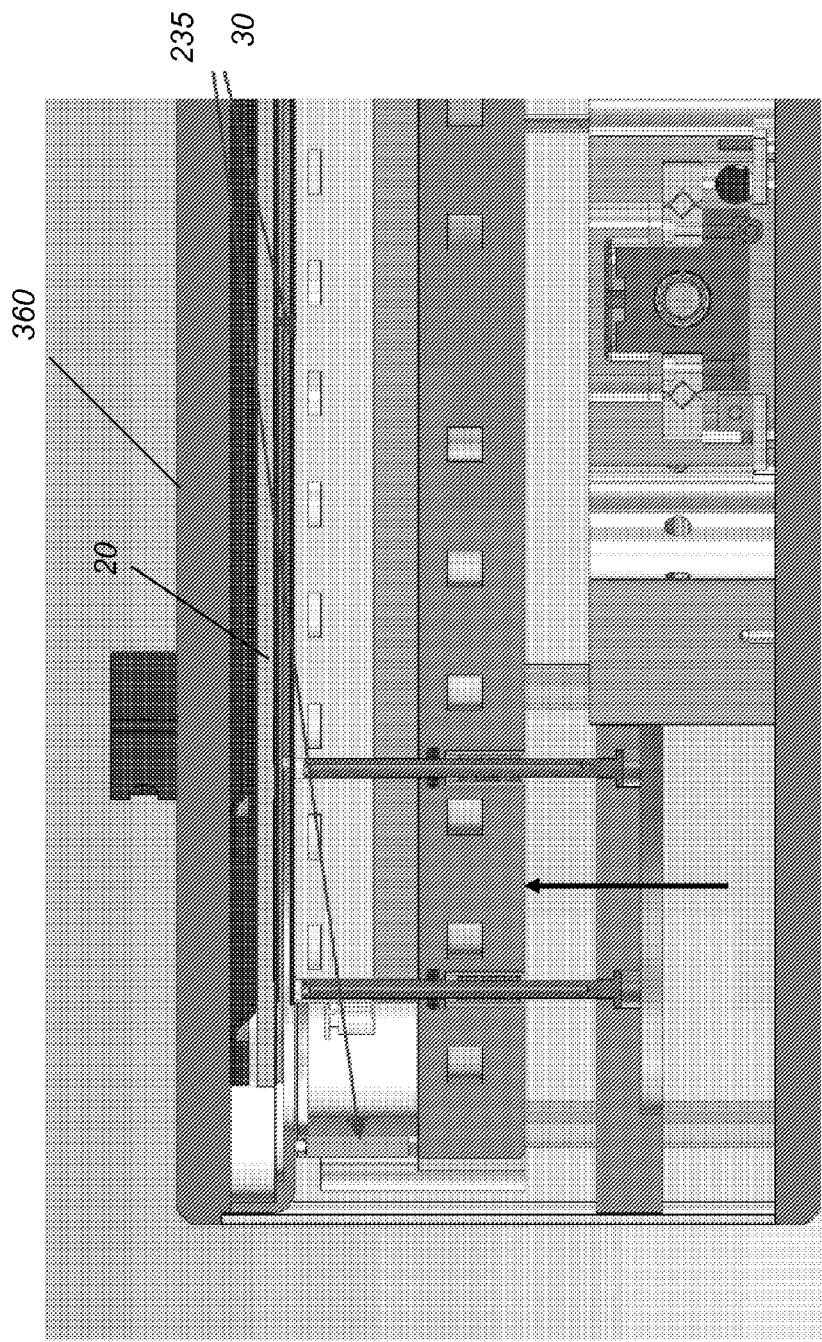


FIG. 22A

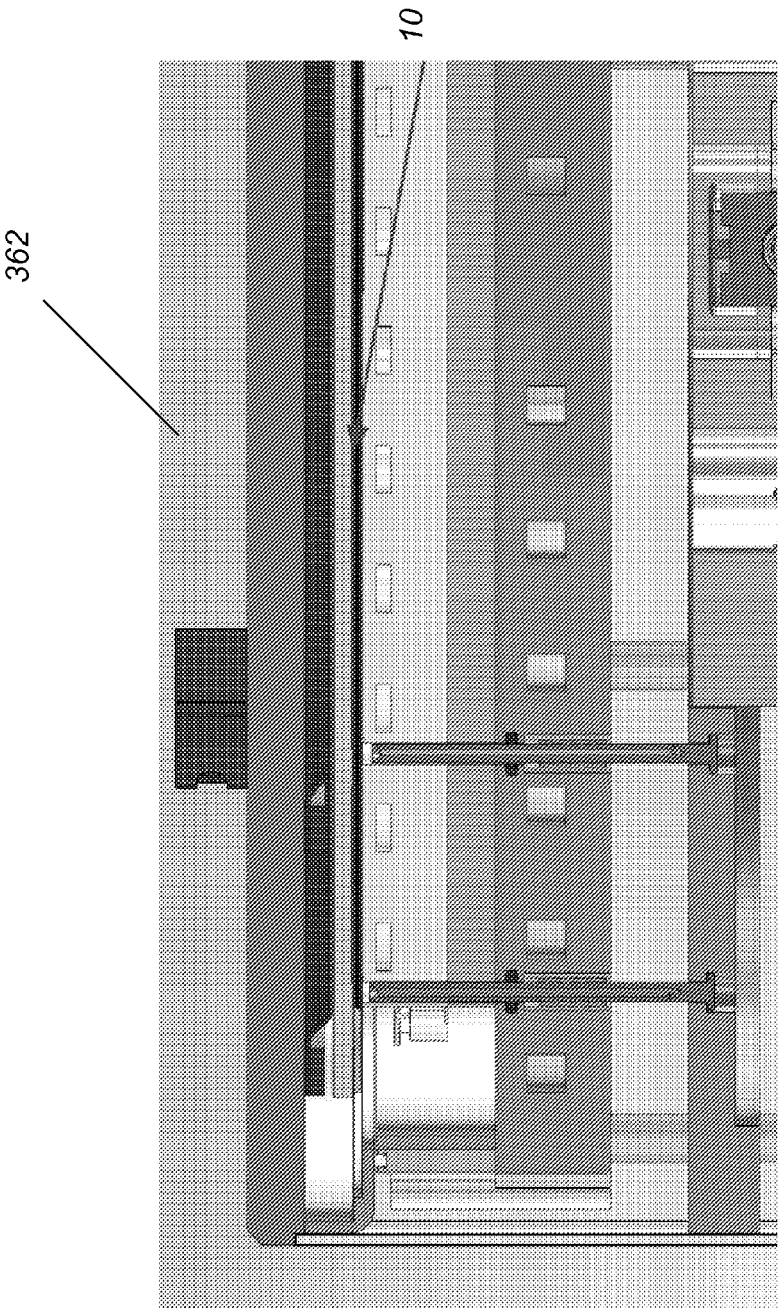


FIG. 22B

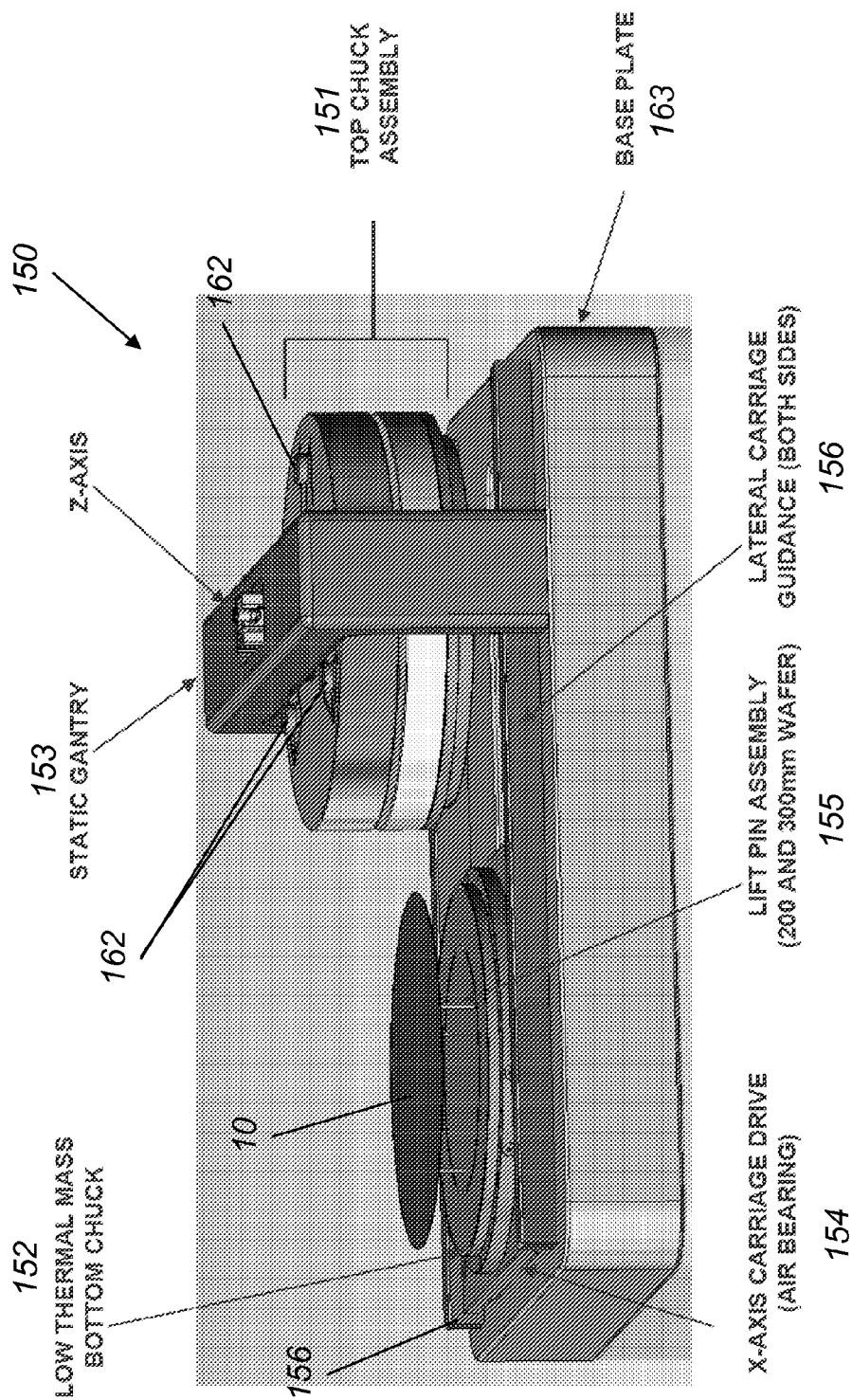


FIG. 23

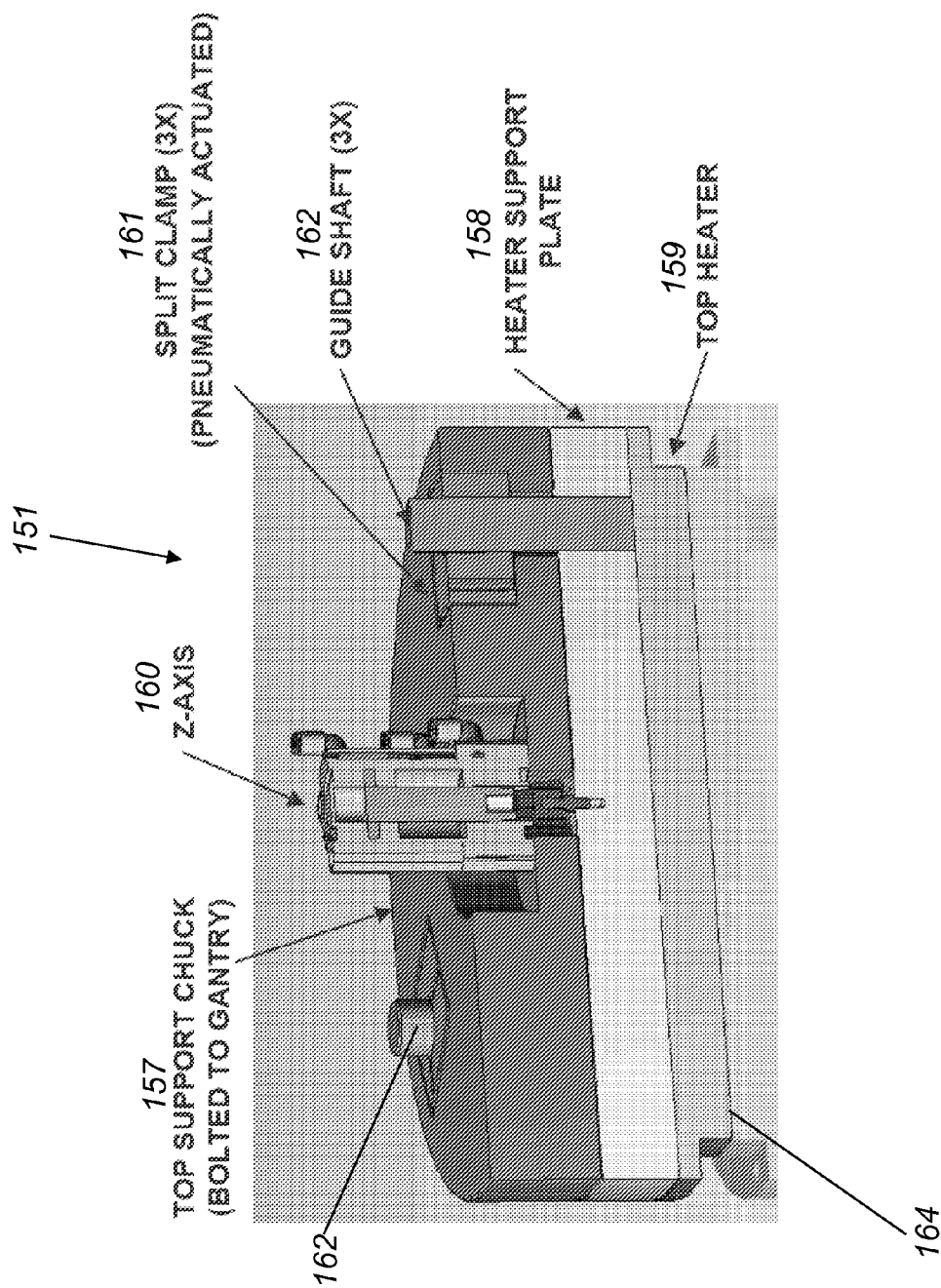


FIG. 24

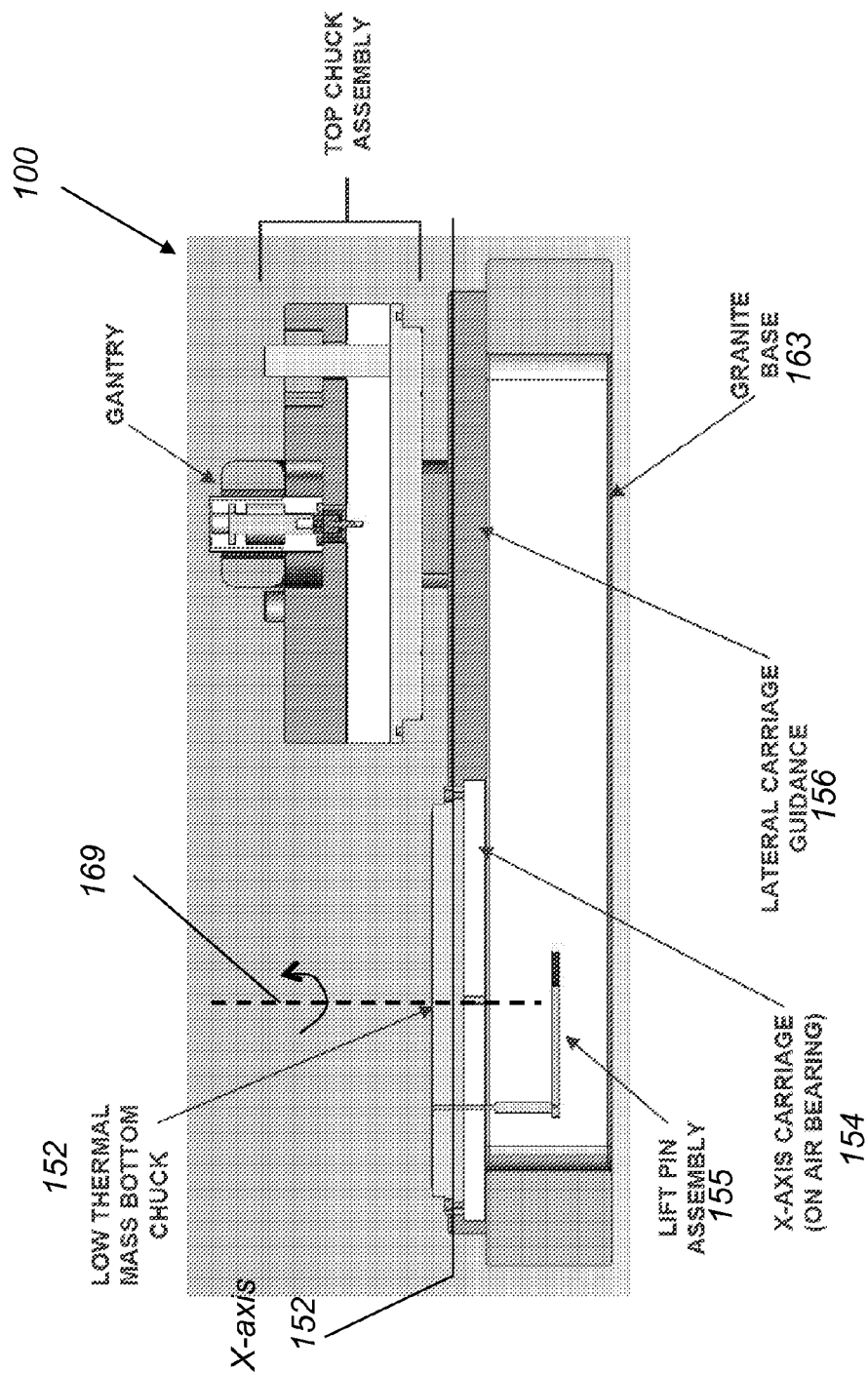


FIG. 25

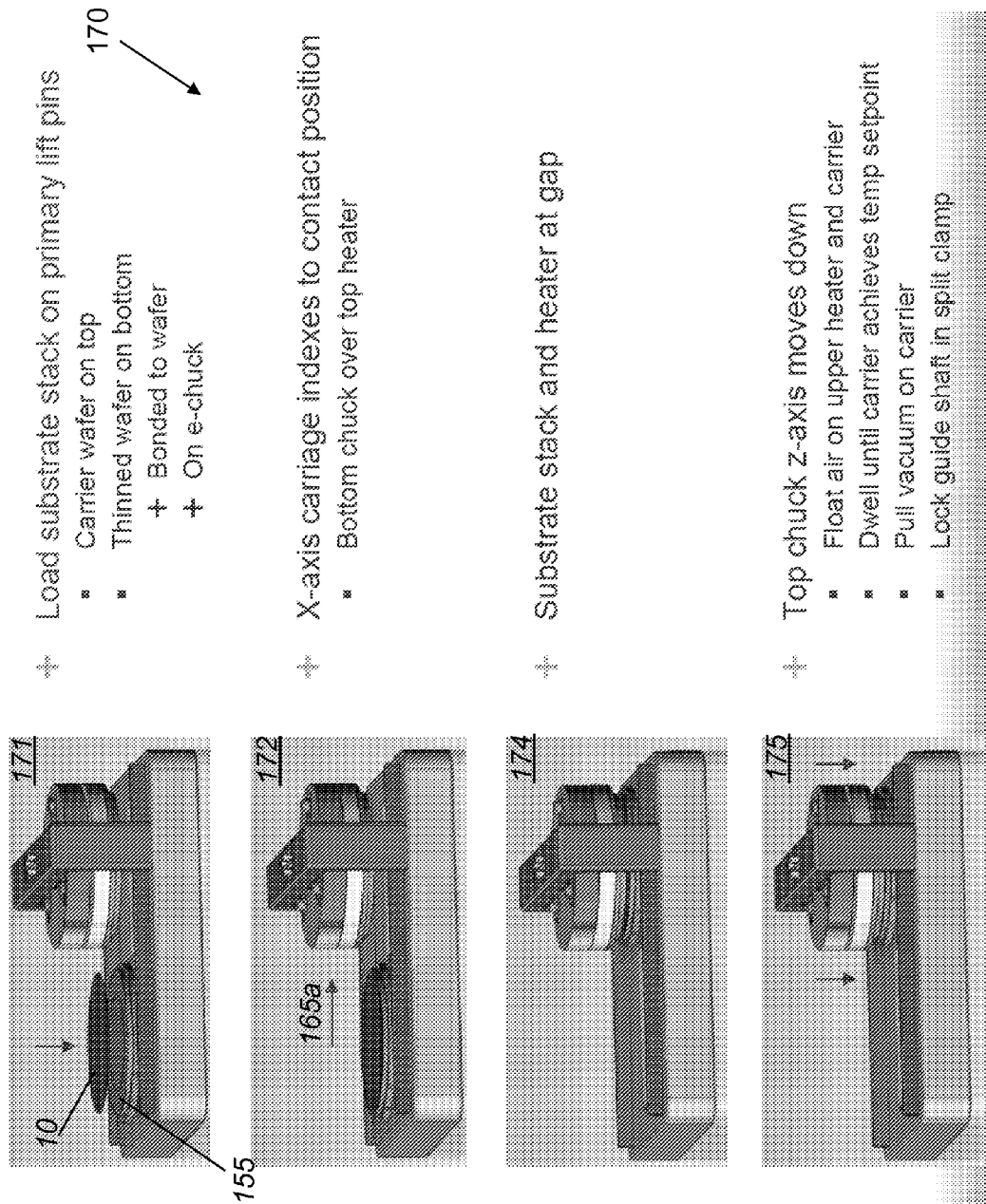
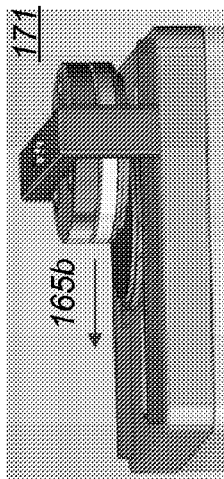
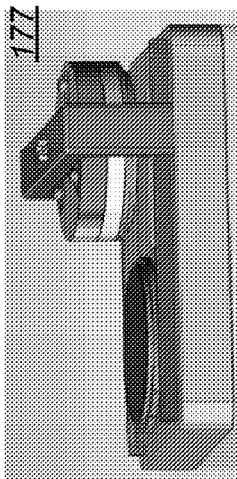


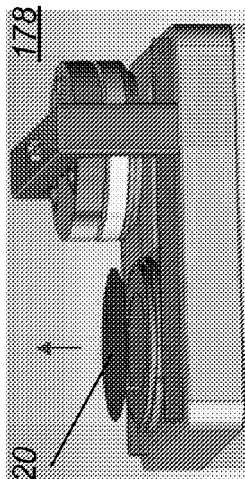
FIG. 26A



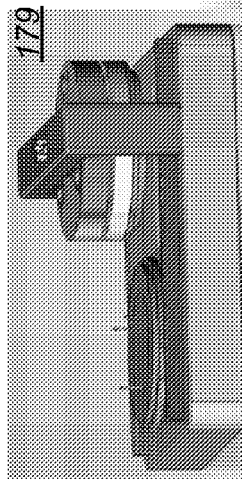
- + Controlled thermal slide separation of substrates
 - * Top chuck assembly rigidly held
 - * Compliant bottom wafer stack
- Twist bottom chuck and
slide X-axis carriage along 165b



- + X-axis carriage indexes to load/unload position
 - * Cool debonded wafer
 - * Enclosure ensures operator safety



- + Primary substrate lift pins up for unload



- + Remove bottom substrate

FIG. 26B

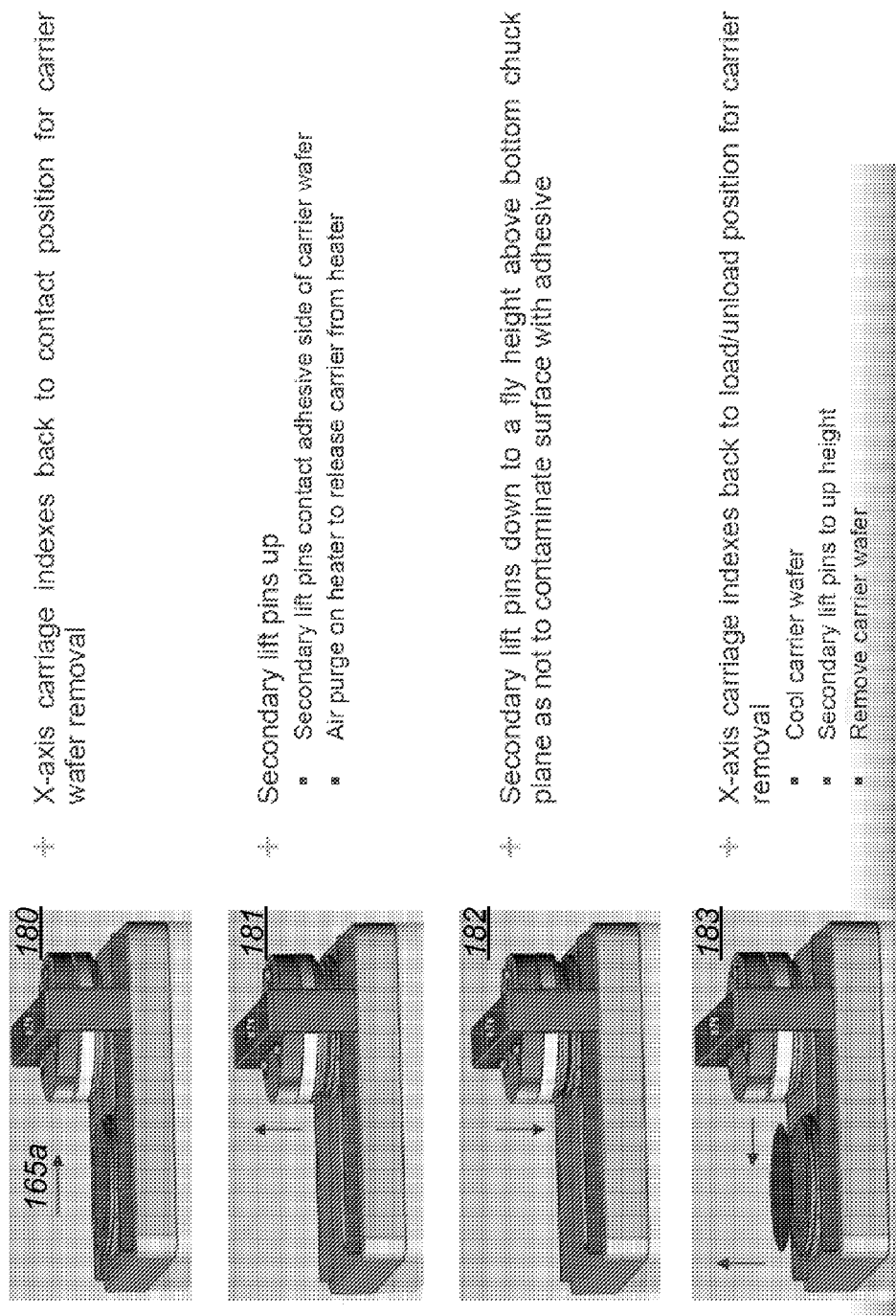


FIG. 26C

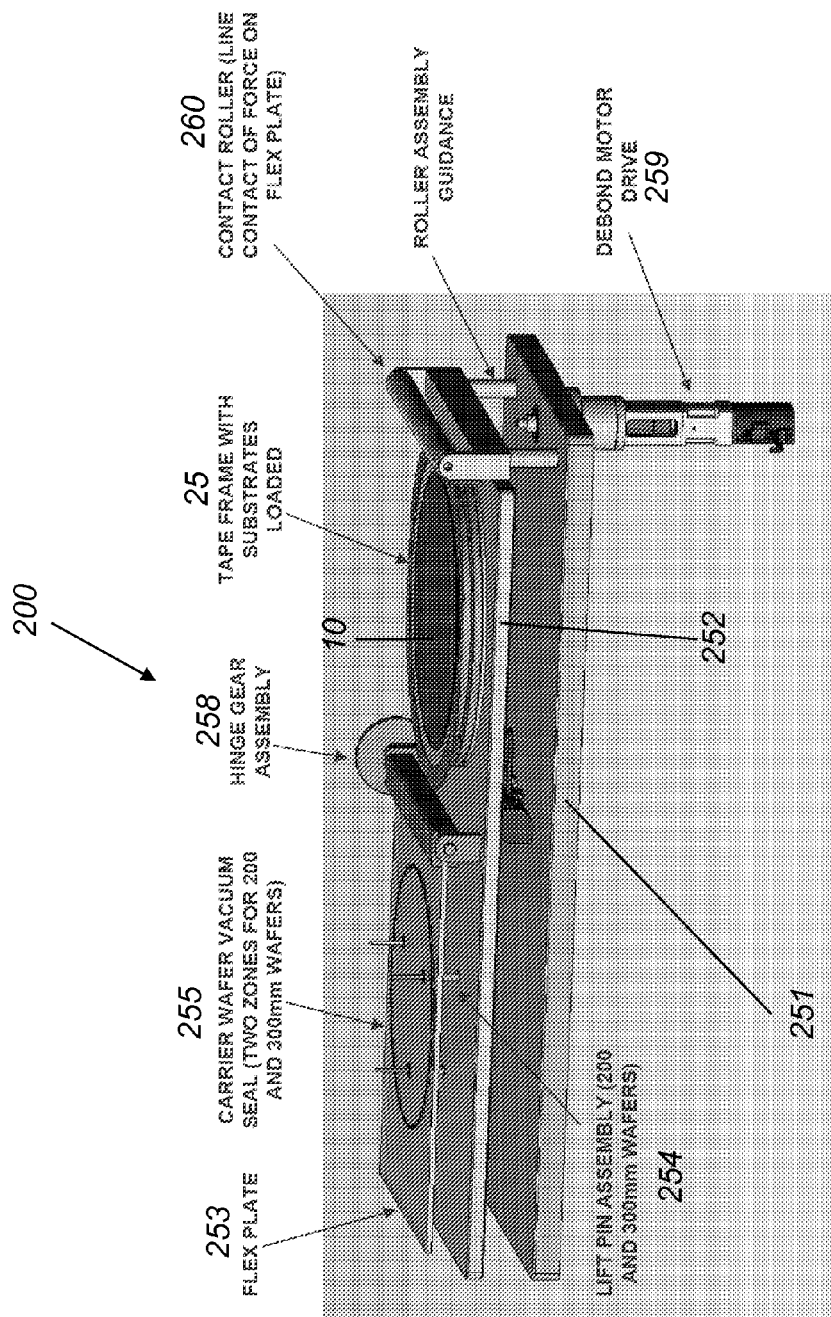


FIG. 27

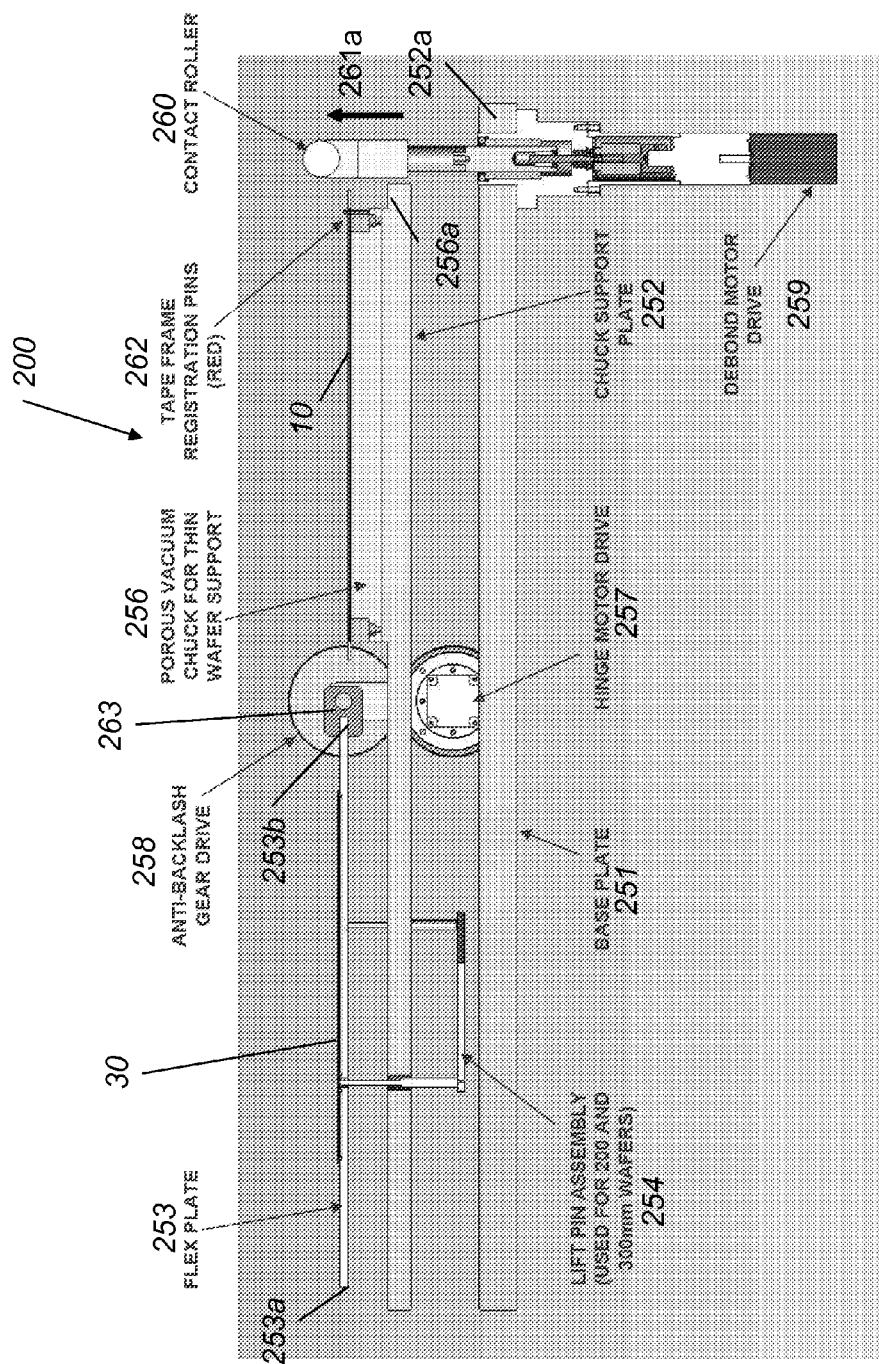


FIG. 28

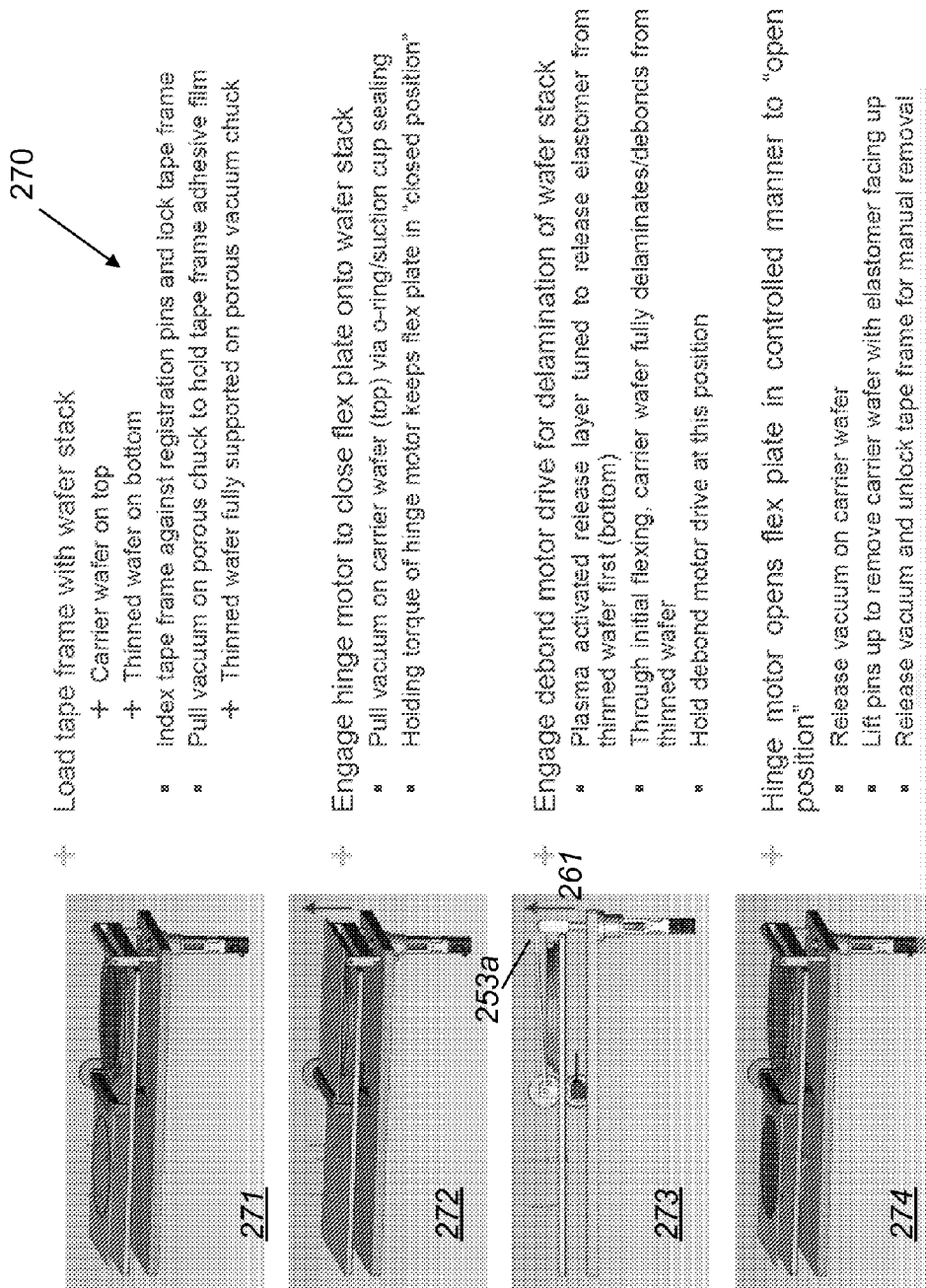


FIG. 29

1

METHOD FOR THERMAL-SLIDE DEBONDING OF TEMPORARY BONDED SEMICONDUCTOR WAFERS

CROSS REFERENCE TO RELATED CO-PENDING APPLICATIONS

This application is a continuation and claims the benefit of U.S. application Ser. No. 12/760,973 filed Apr. 15, 2010 and entitled "APPARATUS FOR THERMAL-SLIDE DEBONDING OF TEMPORARY BONDED SEMICONDUCTOR WAFERS", the contents of which are expressly incorporated herein by reference.

FIELD OF THE INVENTION

The present invention relates to a method for thermal-slide debonding of temporary bonded semiconductor wafers, and more particularly to an industrial-scale thermal-slide debonding method for debonding semiconductor wafers bonded via an adhesive.

BACKGROUND OF THE INVENTION

Several semiconductor wafer processes include wafer thinning steps. In some applications the wafers are thinned down to a thickness of less than 100 micrometers for the fabrication of integrated circuit (IC) devices. Thin wafers have the advantages of improved heat removal and better electrical operation of the fabricated IC devices. In one example, GaAs wafers are thinned down to 25 micrometers to fabricate power CMOS devices with improved heat removal. Wafer thinning also contributes to a reduction of the device capacitance and to an increase of its impedance, both of which result in an overall size reduction of the fabricated device. In other applications, wafer thinning is used for 3D-Integration bonding and for fabricating through wafer vias.

Wafer thinning is usually performed via back-grinding and/or chemical mechanical polishing (CMP). CMP involves bringing the wafer surface into contact with a hard and flat rotating horizontal platter in the presence of a liquid slurry. The slurry usually contains abrasive powders, such as diamond or silicon carbide, along with chemical etchants such as ammonia, fluoride, or combinations thereof. The abrasives cause substrate thinning, while the etchants polish the substrate surface at the submicron level.

The wafer is maintained in contact with the abrasives until a certain amount of substrate has been removed in order to achieve a targeted thickness.

For wafer thicknesses of over 200 micrometers, the wafer is usually held in place with a fixture that utilizes a vacuum chuck or some other means of mechanical attachment.

However, for wafer thicknesses of less than 200 micrometer and especially for wafers of less than 100 micrometers, it becomes increasingly difficult to mechanically hold the wafers and to maintain control of the planarity and integrity of the wafers during thinning. In these cases, it is actually common for wafers to develop microfractures and to break during CMP.

An alternative to mechanical holding of the wafers during thinning involves attaching a first surface of the device wafer (i.e., wafer processed into a device) onto a carrier wafer and thinning down the exposed opposite device wafer surface. The bond between the carrier wafer and the device wafer is temporary and is removed upon completion of the thinning and any other processing steps.

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Several temporary bonding techniques have been suggested including using of adhesive compounds or using of adhesive tapes or layers. Thinned device wafers are debonded from the carrier wafers after processing by chemically dissolving the adhesive layer or by applying heat or radiation in order to decompose the adhesive layer or tape. Extreme care is needed during the debonding process in order to avoid fracture, surface damage, or warping of the extremely thin wafers, typically having a thickness of about 2-80 micrometers. It is desirable to provide an industrial-scale method for debonding adhesively bonded semiconductor wafers that protects extremely thinned wafers from fracture, surface damage or warping.

SUMMARY OF THE INVENTION

In general, in one aspect, the invention features a debonder apparatus for debonding two via an adhesive layer temporary bonded wafers including a top chuck assembly, a bottom chuck assembly, a static gantry supporting the top chuck assembly, an X-axis carriage drive supporting the bottom chuck assembly, and an X-axis drive control. The top chuck assembly includes a heater and a wafer holder. The X-axis drive control drives horizontally the bottom chuck assembly from a loading zone to a process zone under the top chuck assembly and from the process zone back to the loading zone. A wafer pair comprising a carrier wafer bonded to a device wafer via an adhesive layer is placed upon the bottom chuck assembly at the loading zone oriented so that the unbonded surface of the device wafer is in contact with the bottom assembly and is carried by the X-axis carriage drive to the process zone under the top chuck assembly and the unbonded surface of the carrier wafer is placed in contact with the top chuck assembly. The X-axis drive control initiates horizontal motion of the X-axis carriage drive along the X-axis while heat is applied to the carrier wafer via the heater and while the carrier wafer is held by the top chuck assembly via the wafer holder and thereby causes the device wafer to separate and slide away from the carrier wafer.

Implementations of this aspect of the invention may include one or more of the following features. The debonder further includes a lift pin assembly designed to raise and lower wafers placed on the bottom chuck assembly. The debonder further includes a base plate supporting the X-axis carriage drive and the static gantry. The base plate comprises a honeycomb structure and vibration isolation supports or a granite plate. The bottom chuck assembly includes a bottom chuck comprising a low thermal mass ceramic material and is designed to slide horizontally along the X-axis upon the X-axis carriage drive and to twist around the Z-axis. The X-axis carriage drive comprises an air bearing carriage drive. The debonder further includes two parallel lateral carriage guidance tracks guiding the X-axis carriage drive in its horizontal motion along the X-axis. The top chuck assembly further includes a top support chuck bolted to the static gantry, a heater support plate in contact with the bottom surface of the top support chuck, the heater being in contact with the bottom surface of the heater support plate, a top wafer plate in contact with the heater, a Z-axis drive for moving the top wafer plate in the Z-direction and placing the top wafer plate in contact with the unbonded surface of the carrier wafer and a plate leveling system for leveling the top wafer plate and for providing wedge error compensation of the top wafer plate. The wafer holder may be vacuum pulling the carrier wafer. The plate leveling system comprises three guide shafts connecting the heater to the top support chuck and three pneumatically actuated split clamps. The heater comprises two

independently controlled concentric heating zones configured to heat wafers having a diameter of 200 or 300 millimeters, respectively.

In general, in another aspect, the invention features a method for debonding two via an adhesive layer temporary bonded wafers, including the following steps. First, providing a bonder comprising a top chuck assembly, a bottom chuck assembly, a static gantry supporting the top chuck assembly, an X-axis carriage drive supporting the bottom chuck assembly and an X-axis drive control configured to drive horizontally the X-axis carriage drive and the bottom chuck assembly from a loading zone to a process zone under the top chuck assembly and from the process zone back to the loading zone. Next, loading a wafer pair comprising a carrier wafer bonded to a device wafer via an adhesive layer upon the bottom chuck assembly at the loading zone oriented so that the unbonded surface of the device wafer is in contact with the bottom assembly. Next, driving the X-axis carriage drive and the bottom chuck assembly to the process zone under the top chuck assembly. Next, placing the unbonded surface of the carrier wafer in contact with the top chuck assembly and holding the carrier wafer by the top chuck assembly. Next, heating the carrier wafer with a heater comprised in the top chuck assembly. Finally, initiating horizontal motion of the X-axis carriage drive along the X-axis by the X-axis drive control while heat is applied to the carrier wafer and while the carrier wafer is held by the top chuck assembly and thereby causing the device wafer to separate and slide away from the carrier wafer.

The details of one or more embodiments of the invention are set forth in the accompanying drawings and description below. Other features, objects and advantages of the invention will be apparent from the following description of the preferred embodiments, the drawings and from the claims.

BRIEF DESCRIPTION OF THE DRAWINGS

Referring to the figures, wherein like numerals represent like parts throughout the several views:

FIG. 1 is an overview schematic diagram of the improved temporary wafer bonder and debonder system according to this invention;

FIG. 1A is a schematic diagram of temporary wafer bonding process A and debonding process A performed in bonder module A and debonder A of FIG. 1, respectively;

FIG. 1B depicts a schematic cross-sectional view of the bonder module A of FIG. 1 and a list of the process steps for performing the temporary wafer bonding process A of FIG. 1A;

FIG. 2A is a schematic diagram of temporary wafer bonding process B and debonding process B performed in bonder module B and debonder B of FIG. 1, respectively;

FIG. 2B depicts a schematic cross-sectional view of the bonder module B of FIG. 1 and a list of the process steps for performing the temporary wafer bonding process B of FIG. 2A;

FIG. 3A is a schematic diagram of temporary wafer bonding process C and debonding process C performed in bonder module C and debonder C of FIG. 1, respectively;

FIG. 3B depicts a schematic cross-sectional view of the bonder module C of FIG. 1, and a list of the process steps for performing the temporary wafer bonding process C of FIG. 3A;

FIG. 4 depicts a view of a fixture chuck;

FIG. 5 depicts the temporary wafer bonder cluster of FIG. 1;

FIG. 6 depicts a closer view of the upper structure of the temporary wafer bonder cluster of FIG. 5;

FIG. 7 depicts a cross-sectional view of the upper structure of the temporary wafer bonder cluster of FIG. 5;

FIG. 8 depicts the hot plate module of the temporary wafer bonder cluster of FIG. 7;

FIG. 9 depicts a temporary bond module of the wafer bonder cluster of FIG. 7;

FIG. 10 depicts a schematic cross-sectional diagram of the temporary bonder module of FIG. 9;

FIG. 11 depicts a cross-sectional view of the temporary wafer bonder module of FIG. 9 perpendicular to the load direction;

FIG. 12 depicts a cross-sectional view of the temporary wafer bonder module of FIG. 9 in line with the load direction;

FIG. 13 depicts the top chuck leveling adjustment in the temporary wafer bonder module of FIG. 9;

FIG. 14 depicts a cross-sectional view of the top chuck of the temporary wafer bonder module of FIG. 9;

FIG. 15 depicts a detailed cross-sectional view of the temporary wafer bonder module of FIG. 9;

FIG. 16 depicts a wafer centering device with the pre-alignment arms in the open position;

FIG. 17 depicts wafer centering device of FIG. 16 with the pre-alignment arms in the closed position;

FIG. 18A depicts the pre-alignment of a 300 mm wafer;

FIG. 18B depicts the pre-alignment of a 200 mm wafer;

FIG. 19A depicts another wafer centering device for the pre-alignment of a 300 mm wafer;

FIG. 19B depicts the wafer centering device of FIG. 19A for the pre-alignment of a 200 mm wafer;

FIG. 19C depicts another wafer centering device for the pre-alignment of a wafer with the rotating arms in the open position;

FIG. 19D depicts the wafer centering device of FIG. 19C with the rotating arms in the closed position;

FIG. 20A, FIG. 20B and FIG. 20C depict the loading of the non-adhesive substrate and its transfer to the upper chuck;

FIG. 21A, FIG. 21B and FIG. 21C depict the loading of the adhesive substrate and its transfer to the lower chuck;

FIG. 22A and FIG. 22B depict bringing the adhesive substrate in contact with the non-adhesive substrate and the formation of a temporary bond between the two substrates;

FIG. 23 depicts an overview diagram of the thermal slide debonder A of FIG. 1;

FIG. 24 depicts a cross-sectional view of the top chuck assembly of the debonder A of FIG. 23;

FIG. 25 depicts a cross-sectional side view of the debonder A of FIG. 23;

FIG. 26A, FIG. 26B and FIG. 26C depict the thermal slide debonder A operational steps;

FIG. 27 depicts an overview diagram of the mechanical debonder B of FIG. 1;

FIG. 28 depicts a cross-sectional side view of the debonder B of FIG. 27; and

FIG. 29 depicts the debonder B operational steps.

DETAILED DESCRIPTION OF THE INVENTION

Referring to FIG. 1, an improved apparatus for temporary wafer bonding and debonding 100 includes a temporary bonder cluster 110 and a debonder cluster 120. The temporary bonder cluster 110 includes temporary bonder module A, module B, module C, and module D, 210, 310, 410 and 510 respectively. Debonder cluster 120 includes a thermal slide debonder A 150, a mechanical debonder B 250 and a radiation/mechanical debonder C 350. Bonder cluster 110 facili-

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tates the temporary bonding processes A, B, C, and D, **60a**, **70a**, **80a** and **90a**, shown in FIG. 1A, FIG. 2A, FIG. 3A, and FIG. 4, respectively, among others. Debonder cluster **120** facilitates the debonding processes A, B and C, **60b**, **70b**, and **80b**, shown in FIG. 1A, FIG. 2A and FIG. 3A, respectively.

Referring to FIG. 1A, temporary bond process A **60a** includes the following steps. First, device wafer **20** is coated with a protective coating **21** (**62**), the coating is then baked and chilled (**63**) and then the wafer is flipped (**64**). A carrier wafer **30** is coated with an adhesive layer **31** (**65**) and then the coating is baked and chilled (**66**). In other embodiments, a dry adhesive film is laminated onto the carrier wafer, instead of coating an adhesive layer. Next, the flipped device wafer **20** is aligned with the carrier wafer **30** so that the surface of the device wafer with the protective coating **20a** is opposite to the surface of the carrier wafer with the adhesive layer **30a** (**67**) and then the two wafers are bonded (**68**) in temporary bonder module A, shown in FIG. 1B. The bond is a temporary bond between the protective layer **21** and the adhesive layer **31**. In other embodiments, no protective coating is applied onto the device wafer surface and the device wafer surface **20a** is directly bonded with the adhesive layer **31**. Examples of device wafers include GaAs wafers, silicon wafers, or any other semiconductor wafer that needs to be thinned down to less than 100 micrometers. These thin wafers are used in military and telecommunication applications for the fabrication of power amplifiers or other power devices where good heat removal and small power factor are desirable. The carrier wafer is usually made of a non-contaminating material that is thermally matched with the device wafer, i.e., has the same coefficient of thermal expansion (CTE). Examples of carrier wafer materials include silicon, glass, sapphire, quartz or other semiconductor materials. The diameter of the carrier wafer is usually the same as or slightly larger than the diameter of the device wafer, in order to support the device wafer edge and prevent cracking or chipping of the device wafer edge. In one example, the carrier wafer thickness is about 1000 micrometers and the total thickness variation (TTV) is 2-3 micrometers. Carrier wafers are recycled and reused after they are debonded from the device wafer. In one example, adhesive layer **31** is an organic adhesive WaferBOND™ HT-10.10, manufactured by Brewer Science, Ms., USA. Adhesive **31** is applied via a spin-on process and has a thickness in the range of 9 to 25 micrometers. The spin speed is in the range of 1000 to 2500 rpm and the spin time is between 3-60 second. After the spin-on application, the adhesive layer is baked for 2 min at a temperature between 100° C. to 150° C. and then cured for 1-3 minutes at a temperature between 160° C. to 220° C. WaferBOND™ HT-10.10 layer is optically transparent and is stable up to 220° C. After the thinning of the exposed device wafer surface **20b** the carrier wafer **30** is debonded via the debond process A **60b**, shown in FIG. 1A. Debond process A **60b**, includes the following steps. First heating the wafer stack **10** until the adhesive layer **31** softens and the carrier wafer **30** slides off from the thinned wafer (**69**). The WaferBOND™ HT-10.10 debonding time is less than 5 minutes. The thinned wafer **20** is then cleaned, any adhesive residue is stripped away (**52**) and the thinned wafer is placed in a dicing frame **25** (**53**). In some embodiments, a small rotational motion (twisting) of the carrier wafer takes place prior to the sliding translational motion.

The temporary bonding (**68**) of the carrier wafer **30** to the device wafer **20** takes place in temporary bonder module A, **210**. Referring to FIG. 1B, the device wafer **20** is placed in the fixture chuck **202** and the fixture chuck is loaded in the chamber **210**. The carrier wafer **30** is placed with the adhesive layer facing up directly on the bottom chuck **210a** and the two

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wafers **20**, **30** are stacked and aligned. The top chuck **210b** is lowered down onto the stacked wafers and a low force is applied. The chamber is evacuated and the temperature is raised to 200° C. for the formation of the bond between the protective coating layer **21** and the adhesive layer **31**. Next, the chamber is cooled and the fixture is unloaded.

The debond process A **60b** is a thermal slide debond process and includes the following steps, shown in FIG. 1A. The bonded wafer stack **10** is heated causing the adhesive layer **31** to become soft. The carrier wafer is then twisted around axis **169** and then slid off the wafer stack under controlled applied force and velocity (**69**). The separated device wafer **20** is then cleaned (**52**) and mounted onto a dicing frame **25** (**53**).

Referring to FIG. 2A, temporary bond process B **70a** includes the following steps. First, a release layer **22** is formed onto a surface **20a** of the device wafer **20** (**72**). The release layer is formed by first spin-coating a precursor compound onto the wafer device surface **20a** and then performing Plasma Enhanced Chemical Vapor deposition (PECVD) in a commercially available PECVD chamber. In one example, the precursor for the release layer is SemicoSil™, a silicon rubber manufactured by Wacker, Germany. The coated device wafer is then spin coated with an adhesive (**73**) and then flipped (**74**). Next, a soft layer **32** is spin coated on a surface **30a** of the carrier wafer **30** (**76**). In one example, soft layer **32** is a hot temperature cross-linking (HTC) silicone elastomer. Next, the flipped device wafer **20** is aligned with the carrier wafer **30** so that the surface **20a** of the device wafer with the release layer **22** is opposite to the surface **30a** of the carrier wafer with the soft layer **32** (**77**) and then the two wafers are bonded (**78**) in the temporary bonder module B, shown in FIG. 2B. The temporary bond is formed under vacuum of 0.1 mbar, curing temperature between 150° C. to 200° C. and low applied bond force.

Referring to FIG. 2B, the device wafer **20** is placed in the fixture chuck **202** (shown in FIG. 4) with the adhesive layer facing up. Next, spacers **203** are placed on top of the device wafer **20** and then the carrier wafer **30** is placed on top of the spacers and the assembled fixture chuck **202** is transferred to the bonder module B **310**. The chamber is evacuated, the spacers **203** are removed and the carrier wafer **30** is dropped onto the device wafer **20**. In some embodiments, the carrier wafer **30** is dropped onto the device wafer **20** by purging nitrogen or other inert gas through vacuum grooves formed in the upper chuck **222**. In other embodiments the upper chuck **222** is an electrostatic chuck (ESC) and the carrier wafer **30** is dropped onto the device wafer **20** by reversing the polarity of the ESC. Next, a low force is applied by purging the chamber with a low pressure gas and the temperature is raised to 200° C. for the formation of the bond. Next, the chamber is cooled and the fixture is unloaded. In other embodiments, the Z-axis **239** moves up and the stacked wafers **20**, **30** are brought into contact with the upper chuck **222**. The upper chuck **222** may be semi-compliant or non-compliant, as will be described later.

The debond process B **70b** is a mechanical lift debond process and includes the following steps, shown in FIG. 2A. The bonded wafer stack **10** is mounted onto a dicing frame **25** (**54**) and the carrier wafer **30** is mechanically lifted away from the device wafer **20** (**55**). The thinned device wafer **20** remains supported by the dicing frame **25**.

Referring to FIG. 3A, temporary bond process C, **80a** includes the following steps. First, a surface of the device wafer **20** is coated with an adhesive layer **23** (**82**). In one example, adhesive layer **23** is a UV curable adhesive LC3200™, manufactured by 3M Company, MN, USA. The adhesive coated device wafer is then flipped (**84**). Next, a light

absorbing release layer **33** is spin coated on a surface **30a** of the carrier wafer **30** (**86**). In one example, light absorbing release layer **33** is a LC4000, manufactured by 3M Company, MN, USA. Next, the flipped device wafer **20** is aligned with the carrier wafer **30** so that the surface **20a** of the device wafer with the adhesive layer **23** is opposite to the surface **30a** of the carrier wafer **30** with the light absorbing release layer. The two surfaces **20a** and **30a** are brought into contact and the adhesive layer is cured with UV light (**87**). The two wafers are bonded (**88**) in temporary bonder module C **410**, shown in FIG. **3B**. The bond is a temporary bond between the light absorbing release layer **33** and the adhesive layer **23** and is formed under vacuum of 0.1 mbar and low applied bond force. The temporary bonding (**88**) of the carrier wafer to the device wafer occurs in temporary module C, shown in FIG. **3B**.

Referring to FIG. **3B**, the carrier wafer **30** with the laser absorbing release layer LTHC layer is placed on the top chuck **412** and held in place by holding pins **413**. Next, the device wafer **20** is placed on the bottom chuck **414** with the adhesive layer **23** facing up. Next, the wafers **20**, **30** are aligned, the chamber is evacuated, and the top chuck **412** with the carrier wafer **30** is dropped onto the device wafer **20**. A low force is applied for the formation of the bond between the release layer **33** and the adhesive layer **23**. Next, the bonded wafer stack **10** is unloaded and the adhesive is cured with UV light.

Referring back to FIG. **3A**, the debond process C **80b** includes the following steps. The bonded wafer stack **10** is mounted onto a dicing frame **25** (**56**) and the carrier wafer **30** is illuminated with a YAG laser beam. The laser beam causes the separation of the wafer stack along the release layer **33** (**57**) and the separated carrier wafer **30** is mechanically lifted away from the device wafer **20** (**58**). The adhesive layer is peeled away from the device wafer surface **20a** (**59**) and the thinned device wafer **20** remains supported by the dicing frame **25**.

Referring to FIG. **5**, temporary bonder cluster **110** includes a housing **101** having an upper cabinet structure **102** stacked on top of a lower cabinet **103**. The upper cabinet **102** has a service access side **105** and the lower cabinet has leveling adjustments **104** and transport casters **106**. Within the upper cabinet structure **102** the configurable temporary bond process modules **210**, **310**, **410**, **510** are vertically stacked, as shown in FIG. **6**. Hot plate modules **130** and cold plate modules **140** are also vertically stacked on top, below or in-between the process modules **210**, **310**, as shown in FIG. **7**. Additional process modules may be included in order to provide further processing functionalities. Examples of the bond process modules include low applied force module, high applied force module, high temperature and low temperature modules, illumination (UV light or laser) modules, high pressure (gas) module, low (vacuum) pressure module and combinations thereof.

Referring to FIG. **9**-FIG. **12**, temporary bond module **210** includes a housing **212** having a load door **211**, an upper block assembly **220** and an opposing lower block assembly **230**. The upper and lower block assemblies **220**, **230** are movably connected to four Z-guide posts **242**. In other embodiments, less than four or more than four Z-guide posts are used. A telescoping curtain seal **235** is disposed between the upper and lower block assemblies **220**, **230**. A temporary bonding chamber **202** is formed between the upper and lower assemblies **220**, **230** and the telescoping curtain seal **235**. The curtain seal **235** keeps many of the process components that are outside of the temporary bonding chamber area **202** insulated from the process chamber temperature, pressure, vacuum, and atmosphere. Process components outside of the

chamber area **202** include guidance posts **242**, Z-axis drive **243**, illumination sources, mechanical pre-alignment arms **460a**, **460b** and wafer centering jaws **461a**, **461b**, among others. Curtain **235** also provides access to the bond chamber **202** from any radial direction.

Referring to FIG. **11**, the lower block assembly **230** includes a heater plate **232** supporting the wafer **20**, an insulation layer **236**, a water cooled support flange **237** a transfer pin stage **238** and a Z-axis block **239**. Heater plate **232** is a ceramic plate and includes resistive heater elements **233** and integrated air cooling **234**. Heater elements **233** are arranged so the two different heating zones are formed. A first heating zone **233B** is configured to heat a 200 mm wafer or the center region of a 300 mm wafer and a second heating zone **233A** is configured to heat the periphery of the 300 mm wafer. Heating zone **233A** is controlled independently from heating zone **233B** in order to achieve thermal uniformity throughout the entire bond interface **405** and to mitigate thermal losses at the edges of the wafer stack. Heater plate **232** also includes two different vacuum zones for holding wafers of 200 mm and 300 mm, respectively. The water cooled thermal isolation support flange **237** is separated from the heater plate by the insulation layer **236**. The transfer pin stage **238** is arranged below the lower block assembly **230** and is movable supported by the four posts **242**. Transfer pin stage **238** supports transfer pins **240** arranged so that they can raise or lower different size wafers.

In one example, the transfer pins **240** are arranged so that they can raise or lower 200 mm and 300 mm wafers. Transfer pins **240** are straight shafts and, in some embodiments, have a vacuum feed opening extending through their center, as shown in FIG. **15**. Vacuum drawn through the transfer pin openings holds the supported wafers in place onto the transfer pins during movement and prevents misalignment of the wafers. The Z-axis block **239** includes a precision Z-axis drive **243** with ball screw, linear cam design, a linear encoder feedback **244** for submicron position control, and a servomotor **246** with a gearbox, shown in FIG. **12**.

Referring to FIG. **13**, the upper block assembly **220** includes an upper ceramic chuck **222**, a top static chamber wall **221** against which the curtain **235** seals with seal element **235a**, a 200 mm and a 300 mm membrane layers **224a**, **224b**, and three metal flexure straps **226** arranged circularly at 120 degrees. The membrane layers **224a**, **224b**, are clamped between the upper chuck **222** and the top housing wall **213** with clamps **215a**, **215b**, respectively, and form two separate vacuum zones **223a**, **223b** designed to hold 200 mm and 300 mm wafers, respectively, as shown in FIG. **14**. Membrane layers **224a**, **224b** are made of elastomer material or metal bellows. The upper ceramic chuck **222** is highly flat and thin. It has low mass and is semi-compliant in order to apply uniform pressure upon the wafer stack **10**. The upper chuck **222** is lightly pre-loaded with membrane pressure against three adjustable leveling clamp/drive assemblies **216**.

Clamp/drive assemblies **216** are circularly arranged at 120 degrees. The upper chuck **222** is initially leveled while in contact with the lower ceramic heater plate **232**, so that it is parallel to the heater plate **232**. The three metal straps **226** act a flexures and provide X-Y-T (Theta) positioning with minimal Z-constraint for the upper chuck **222**. The clamp/drive assemblies **216** also provide a spherical Wedge Error Compensating (WEC) mechanism that rotates and/or tilts the ceramic chuck **222** around a center point corresponding to the center of the supported wafer without translation. In other embodiments, the upper ceramic chuck **222** positioning is accomplished with fixed leveling/locating pins, against which the chuck **222** is lashed.

The loading and pre-alignment of the wafers is facilitated with the mechanical centering device **460**, shown in FIG. 16. Centering device **460** includes two rotatable pre-alignment arms **460a**, **460b** and a linearly moving alignment arm **460c**, shown in the open position in FIG. 16 and in the closed position in FIG. 17. At the ends of each arm **460a**, **460b** there are mechanical jaws **461a**, **461b**. The mechanical jaws **461a**, **461b** have tapered surfaces **462** and **463** that conform to the curved edge of the 300 mm wafer and 200 mm wafer, respectively, as shown in FIG. 18A and FIG. 18B. The linearly moving arm **460c** has a jaw **461c** with a tapered curved inner surface that also conforms to the curved edge of circular wafers. Rotating arms **460a**, **460b** toward the center **465** of the support chuck **464** and linearly moving arm **460c** toward the center **465** of the support chuck **464** brings the tapered surfaces of the mechanical jaws **461a**, **461b** and the tapered curved inner surface of jaw **461c** in contact with the outer perimeter of the wafer and centers the wafer on the support chuck **464**. The three arms **460a**, **460b**, **460c** are arranged at 120 degrees around the support chuck **464**. In another embodiment, the centering device **460** includes three rotatable pre-alignment arms, and at the ends of each arm there are mechanical jaws, as shown in FIG. 18A and FIG. 18B. Rotating the arms toward the center of the support chuck **464** brings the tapered surfaces of the mechanical jaws in contact with the outer perimeter of the wafer and centers the wafer on the support chuck **464**.

In another embodiment, the loading and pre-alignment of the wafers is facilitated with wafer centering device **470**, shown in FIG. 19A and FIG. 19B. Wafer centering device **470** includes three centering linkages **471**, **472**, **473**. Centering linkage **471** includes a rectilinear mid-position air bearing or mechanical slide **471a** that moves the wafer **30** in the Y-direction. Centering linkages **472**, **473**, include rotating centering arms **472a**, **473a**, that rotate clockwise and counterclockwise, respectively. The motions of the centering linkages **471**, **472**, **473**, are synchronized by the use of a cam plate **474** with two linear cam profiles **474a**, **474b**. Cam profile **474a** provides rectilinear motion for the mid-position centering arm **471** and cam profile **474b** provides rectilinear motion for left and right centering arm push rods **472b**, **473b**. The rectilinear motion of the push rods **472b**, **473b**, is translated into rotary motion at the cam/cam follower interface at the centering arms **472a**, **473a**, respectively. The cam plate is **474** fixed to a linear slide that is driven in a rectilinear motion (X-axis motion) by an electric motor or pneumatic actuation. A Linear Variable Differential Transformer (LVDT) or another electrical sensor at the mid-position centering arm **471** mechanism provides distance feedback, which indicates that the centering devices are stopped against the wafer edge. There is a spring preload on the centering device **471a**, and when the spring preload is overtaken the LVDT registers a displacement.

In yet another embodiment, the loading and pre-alignment of the wafer **30** is facilitated with wafer centering device **480**, shown in FIG. 19C and FIG. 19D. Wafer centering device **480** includes three centering linkages **481**, **482**, **483**. Centering linkage **481** includes a rectilinear mid-position air bearing or mechanical slide **481a** that moves the wafer **30** in the Y-direction. Centering linkages **482**, **483**, include rotating centering arms **482a**, **483a**, that rotate clockwise and counterclockwise, respectively. The motions of the centering linkages **481**, **482**, **483**, are synchronized by the use of two plates **484**, **485** that include linear cam profiles **484a**, **484b**, respectively. Cam profiles **484a**, **485a** provide rectilinear motion for left and right centering arm push rods **482**, **483**, respectively. The rectilinear motion of the push rods **482**, **483**, is translated into

rotary motion at the cam/cam follower interface at the centering arms **486a**, **486b**, respectively. Plates **484**, **485** are connected to linear slide **481a** via rods **481a**, **481b**, respectively. The linear motion of slide **481a** in the Y direction is translated via the rods **486a**, **486b**, into linear motion of plates **484**, **485**, respectively, along the X-axis, as shown in FIG. 19D.

Referring to FIG. 20A, FIG. 20B, FIG. 20C, the temporary bonding operation with the bonder module **210** includes the following steps. First, the non-adhesive substrate is loaded onto the transfer pins **240a** by a robot end effector (**350**). In this case the substrate is a 300 mm wafer and is supported by the 300 mm pins **240a**, whereas the 200 mm pins **240b** are shown to be slightly lower than the 300 mm pins **240a**. Next, the mechanical taper jaws **461a**, **461b**, move into position around the wafer and the transfer pins **240a** move down (**352**). The transfer pins have vacuum and purge functions. The purge function allows the wafer to float during the centering cycle and the vacuum function holds the wafer when the centering is complete. The tapered "funnel" jaws **461a**, **461b**, **461c**, drive the wafer to the center as it is lowered via the transfer pins **240a**. Jaws **461a**, **461b**, **461c**, are designed to accommodate and pre-align any size wafers, including 200 mm and 300 mm, shown in FIGS. 19 and 18, respectively. Next, the centering jaws **461a**, **461b**, **461c** retract and the transfer pins move up to place the top substrate **20** on the upper vacuum chuck **222**, as shown in FIG. 20C (**354**). Next, a second adhesive coated substrate **30** is loaded face up onto the transfer pins **240a** by the robot end effector (**356**), shown in FIG. 21A (**356**). Next, the mechanical taper jaws **460** move into position around the wafer **30** and the transfer pins **240a** move down and then up (**358**), shown in FIG. 21B. The centering jaws **461a**, **461b** retract and the transfer pins **240a** move down to place the substrate **30** on the bottom vacuum chuck **232** (**359**), shown in FIG. 21C. Next, the lower heater stage **230** moves up to form a close process gap between the top **20** and bottom **30** substrates and the curtain seal **235** is closed to form the temporary bonding chamber **202** (**360**), shown in FIG. 22A. An initial deep vacuum is drawn (10-4 mbar) in the temporary bonding chamber **202** while the top substrate with **20** is held via mechanical fingers. Once the set vacuum level is reached the chamber pressure is raised slightly to about 5 mbar to generate a differential vacuum pressure that holds the top substrate **20** to the upper chuck **222**. The Z-axis stage **239** moves further up to bring the bottom substrate **30** in contact with the top substrate **20**, as shown in FIG. 22B (**362**). The top chuck **222** is lifted off from the stops **216** by this motion (**362**). Next, force is applied via the top membrane **224a** and bottom top chuck **232** and the wafer stack **10** is heated to the process temperature (**364**). In one example, the applied force is in the range between 500 N to 8000 N and the process temperature is 200 C. In cases where single sided heating is used, the wafer stack **10** is compressed with the membrane pressure to ensure good thermal transfer. After the end of the treatment, the bonded wafer stack **10** is cooled and unloaded with the help of the transfer pins and the robot end effector (**366**).

In the above described case, the Z-axis moves up to contact the thin, semi-compliant upper chuck **222**/membrane **224** design. In this embodiment, the adhesive layer controls the TTV/tilt by applying pressure only in the direction perpendicular to the bond interface via the membranes/chuck flexures and by using a semi compliant chuck to conform to the adhesive topography. In other embodiments, the Z-axis moves up to contact a non-compliant chuck. In these cases the Z-axis motion controls the final thickness of the adhesive layer and forces the adhesive to conform to the rigid flat chuck

222. The adhesive layer thickness may be controlled by using a Z-axis position control, pre-measured substrate thicknesses and known adhesive thicknesses. In yet other embodiments, a compliant layer is installed on the bottom chuck 232 and the adhesive is pre-cured or its viscosity is adjusted. In yet other

Referring to FIG. 23, thermal slide debonder 150 includes a top chuck assembly 151, a bottom chuck assembly 152, a static gantry 153 supporting the top chuck assembly 151, an X-axis carriage drive 154 supporting the bottom chuck assembly 152, a lift pin assembly 155 designed to raise and lower wafers of various diameters including diameters of 200 mm and 300 mm, and a base plate 163 supporting the X-axis carriage drive 154 and gantry 153.

Referring to FIG. 24, the top chuck assembly 151 includes a top support chuck 157 bolted to gantry 153, a heater support plate 158 in contact with the bottom surface of the top support chuck 157, a top heater 159 in contact with the bottom surface of the heater plate 158, a Z-axis drive 160 and a plate leveling system for leveling the upper wafer plate/heater bottom surface 164. The plate leveling system includes three guide shafts 162 that connect the top heater 159 to the top support chuck 157 and three pneumatically actuated split clamps 161. The plate leveling system provides a spherical Wedge Error Compensating (WEC) mechanism that rotates and/or tilts the upper wafer plate 164 around a center point corresponding to the center of the supported wafer without translation. The heater 159 is a steady state heater capable to heat the supported wafer stack 10 up to 350° C. Heater 159 includes a first heating zone configured to heat a 200 mm wafer or the center region of a 300 mm wafer and a second heating zone configured to heat the periphery of the 300 mm wafer. The first and second heating zones are controlled independently from each other in order to achieve thermal uniformity throughout the entire bond interface of the wafer stack and to mitigate thermal losses at the edges of the wafer stack. The heater support plate 158 is water cooled in order to provide thermal isolation and to prevent the propagation of any thermal expansion stresses that may be generated by the top heater 159.

Referring to FIG. 25, the bottom chuck 152 is made of a low thermal mass ceramic material and is designed to slide along the X-axis on top of the air bearing carriage drive 154. The carriage drive 154 is guided in this X-axis motion by two parallel lateral carriage guidance tracks 156. Bottom chuck 152 is also designed to rotate along its Z-axis 169. A Z-axis rotation by a small angle (i.e., twisting) is used to initiate the separation of the wafers, as will be described below. The base plate 163 is vibration isolated. In one example, base plate is made of granite. In other examples base plate 156 has a honeycomb structure and is supported by pneumatic vibration isolators (not shown).

Referring to FIG. 26A, FIG. 26B, FIG. 26C, the debonding operation with the thermal slide debonder 150 of FIG. 23 includes the following steps. First, the temporary bonded wafer stack 10 is loaded on the primary lift pins 155 arranged so that the carrier wafer 30 is on the top and the thinned device wafer 20 is on the bottom (171). Next, the wafer stack 10 is lowered so that the bottom surface of the thinned device wafer 20 is brought into contact with the bottom chuck 152 (172). The bottom chuck 152 is then moved along the 165a direction until it is under the top heater 159 (174). Next, the Z-axis 160 of the top chuck 151 moves down and the bottom surface 164 of the top heater 159 is brought into contact with the top surface of the carrier wafer 30 and then air is floated on top heater 159 and carrier wafer 30 until the carrier wafer stack 30 reaches a set temperature. When the set temperature is

reached, vacuum is pulled on the carrier wafer 30 so that is held by the top chuck assembly 151 and the guide shafts 162 are locked in the split clamps 162 (175). At this point the top chuck 151 is rigidly held while the bottom chuck 152 is compliant and the thermal slide separation is initiated (176) by first twisting the bottom chuck 152 and then moving the X-axis carriage 154 toward the 165b direction away from the rigidly held top chuck assembly 151 (177). The debonded thinned device wafer 20 is carried by the X-axis carriage 154 to the unload position where it is lifted up by the pins (178) for removal (179). Next, the X-axis carriage 154 moves back along direction 165a (180). Upon reaching the position under the top chuck assembly 151, the lift pins 155 are raised to contact the adhesive side of the carrier wafer 30 and air is purged onto the heater plate 159 to release the carrier wafer from it (181). The lift pins 155 are lowered to a height just above the bottom chuck plane so as to not contaminated the bottom chuck top surface with the adhesive (182) and the X-axis carriage 154 moves along 165b back to the unload position. The carrier wafer is cooled and then removed (183).

Referring to FIG. 2A, mechanical debonder B 250 debonds the carrier wafer 30 from the thinned device wafer 20 by mechanically lifting an edge 31 of the carrier wafer 30 away from the thinned device wafer 20. Prior to the debonding process the temporary bonded wafer stack 10 is attached to a frame 25, and upon separation the thinned wafer remains supported by the frame 25. Referring to FIG. 27 and FIG. 28, debonder 250 includes a flex plate 253 with a two zone circular vacuum seal 255. Seal 255 includes two zones, one for a sealing a 200 mm wafer placed within the area surrounded by the seal and a second for sealing a 300 mm wafer within the area surrounded by the seal. Seal 255 is implemented either with an O-ring or with suction cups. A lift pin assembly 254 is used to raise or lower the separated carrier wafer 30 that is transported by the flex plate 253. Debonder 250 also includes a vacuum chuck 256. Both the vacuum chuck 256 and the flex plate 253 are arranged next to each other upon a support plate 252, which in turn is supported by the base plate 251. Flex plate 253 has an edge 253b connected to a hinge 263 that is driven by a hinge motor drive 257. Vacuum chuck 256 is made of a porous sintered ceramic material and is designed to support the separated thin wafer 20. Hinge motor drive 257 is used to drive the flex plate 253 upon the wafer stack 10 after the wafer stack 10 has been loaded on the vacuum chuck 256. An anti-backlash gear drive 258 is used to prevent accidental backing of the flex plate 253. A debond drive motor 259 is attached at the edge 251a of the base plate 251 and next to the edge of the chuck support plate 252a. Debond drive motor 259 moves a contact roller 260 vertical to the plane of the base plate 251 in direction 261 and this motion of the contact roller 260 lifts the edge 253a of the flex plate 253 after the flex plate has been placed upon the loaded wafer stack 10, as will be described below.

Referring to FIG. 29, the debonding operation 270 with the debonder 250 includes the following steps. First, The tape frame 25 with the wafer stack 10 is loaded upon the vacuum chuck 256, so that the carrier wafer 30 is on the top and the thinned wafer 20 is on the bottom (271). The tape frame 25 is indexed against the frame registration pins 262, shown in FIG. 28, and the position of the tape frame 25 is locked. Next, vacuum is pulled through the porous vacuum chuck 256 to hold the tape frame adhesive film. Next, the hinge motor 257 is engaged to transport the flex plate 253 onto the loaded wafer stack, so that it is in contact with the back of the carrier wafer 30 (272). Upon reaching the position upon the carrier wafer 30, vacuum is pulled on the carrier wafer top via the seal 255. The torque of the hinge motor 257 is kept constant to

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maintain the flex plate 253 in this “closed position”. Next, the debond motor 259 is engaged to move the contact roller 260 up in the direction 261a and to push the edge 253a of the flex plate 253 up (273). This upward motion of the flex plate edge 253a bents (or flexes) slightly the carrier wafer 30 and cause the wafer stack 10 to delaminate along the release layer 32 and thereby to separate the carrier wafer 30 from the thinned wafer 20. Silicon wafers break or cleave much easier along the (110) crystallographic plane than any other orientation. Therefore, the carrier wafer 30 is fabricated on a (110) plane so that its 110 direction is perpendicular to the push direction 261a, thereby preventing breaking of the wafer 30 during delamination. The thinned wafer 20 remains attached to the tape frame 25, which is held by the vacuum chuck 256. Through this step the debond motor 259 is held constant in position. Next, the hinge motor drive 257 opens the flex plate 253 with the attached separated carrier wafer 30 in the “open position”, in a controlled manner (274). The flex plate vacuum is released thereby releasing the carrier wafer 30. Next, the lift pins 254 are moved up to raise the carrier wafer 30 oriented so that the release layer 32 is facing up and then the carrier wafer 30 is removed. Next, the vacuum through the porous vacuum chuck 256 is released and the tape 25 with the attached thinned wafer 20 is removed.

Several embodiments of the present invention have been described. Nevertheless, it will be understood that various modifications may be made without departing from the spirit and scope of the invention. Accordingly, other embodiments are within the scope of the following claims.

What is claimed is:

1. A method for debonding two via an adhesive layer temporary bonded wafers, comprising:

providing a debonder comprising a top chuck assembly, a bottom chuck assembly, a static gantry supporting the top chuck assembly, an X-axis carriage drive supporting the bottom chuck assembly and an X-axis drive control configured to drive horizontally the X-axis carriage drive and the bottom chuck assembly from a loading zone to a process zone under the top chuck assembly and from the process zone back to the loading zone;

loading a wafer pair comprising a carrier wafer bonded to a device wafer via an adhesive layer upon said bottom chuck assembly at the loading zone oriented so that an unbonded surface of the device wafer is in contact with the bottom assembly;

driving said X-axis carriage drive and said bottom chuck assembly to the process zone under the top chuck assembly;

placing an unbonded surface of the carrier wafer in contact with the top chuck assembly and holding said carrier wafer by said top chuck assembly;

heating said carrier wafer with a heater comprised in said top chuck assembly to a temperature around or above said adhesive layer's melting point;

initiating horizontal motion of said X-axis carriage drive along the X-axis by said X-axis drive control while heat is applied to said carrier wafer and while said carrier wafer is held by said top chuck assembly and said device wafer is held by said bottom chuck assembly and thereby causing the device wafer to separate and slide away from the carrier wafer; and

wherein said bottom chuck assembly comprises a bottom chuck comprising a ceramic material and is designed to slide horizontally along the X-axis upon said X-axis carriage drive and to twist around the Z-axis.

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2. The method of claim 1, further comprising raising and lowering said wafer pair onto the bottom chuck assembly via a lift pin assembly.

3. The method of claim 1, wherein said debonder further comprises a base plate supporting the X-axis carriage drive and the static gantry.

4. The method of claim 3, wherein said base plate comprises a honeycomb structure and vibration isolation supports.

5. The method of claim 3, wherein said base plate comprises a granite plate.

6. The method of claim 1, further comprising twisting the device wafer at the same time said horizontal motion is initiated.

7. The method of claim 1, wherein said X-axis carriage drive comprises an air bearing carriage drive.

8. The method of claim 1, wherein said debonder further comprises two parallel lateral carriage guidance tracks guiding said X-axis carriage drive in its horizontal motion along the X-axis.

9. The method of claim 1, wherein said top chuck assembly further comprises:

a top support chuck bolted to the static gantry;

a heater support plate in contact with the bottom surface of the top support chuck;

said heater being in contact with the bottom surface of the heater support plate;

a top wafer plate in contact with the heater;

a Z-axis drive for moving the top wafer plate in the Z-direction and placing the top wafer plate in contact with the unbonded surface of the carrier wafer; and

a plate leveling system for leveling the top wafer plate and for providing wedge error compensation of the top wafer plate.

10. The method of claim 1, wherein said carrier wafer is held by said top chuck assembly via vacuum.

11. The method of claim 1, wherein said plate leveling system comprises three guide shafts connecting said heater to said top support chuck and three pneumatically actuated split clamps.

12. The method of claim 1, wherein said heater comprises two independently controlled concentric heating zones configured to heat wafers having a diameter of 200 or 300 millimeters, respectively.

13. A method for debonding two via an adhesive layer temporary bonded wafers, comprising:

providing a debonder comprising a top chuck assembly, a bottom chuck assembly, a static gantry supporting the top chuck assembly, an X-axis carriage drive supporting the bottom chuck assembly and an X-axis drive control configured to drive horizontally the X-axis carriage drive and the bottom chuck assembly from a loading zone to a process zone under the top chuck assembly and from the process zone back to the loading zone;

loading a wafer pair comprising a carrier wafer bonded to a device wafer via an adhesive layer upon said bottom chuck assembly at the loading zone oriented so that an unbonded surface of the device wafer is in contact with the bottom assembly;

driving said X-axis carriage drive and said bottom chuck assembly to the process zone under the top chuck assembly;

placing an unbonded surface of the carrier wafer in contact with the top chuck assembly and holding said carrier wafer by said top chuck assembly;

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heating said carrier wafer with a heater comprised in said top chuck assembly to a temperature around or above said adhesive layer's melting point;

initiating horizontal motion of said X-axis carriage drive along the X-axis by said X-axis drive control while heat is applied to said carrier wafer and while said carrier wafer is held by said top chuck assembly and said device wafer is held by said bottom chuck assembly and thereby causing the device wafer to separate and slide away from the carrier wafer; and

wherein said debonder further comprises a base plate supporting the X-axis carriage drive and the static gantry; and

wherein said base plate comprises a honeycomb structure and vibration isolation supports.

14. The method of claim **13**, wherein said bottom chuck assembly comprises a bottom chuck comprising a ceramic material and is designed to slide horizontally along the X-axis upon said X-axis carriage drive and to twist around the Z-axis.

15. A method for debonding two via an adhesive layer temporary bonded wafers, comprising:

providing a debonder comprising a top chuck assembly, a bottom chuck assembly, a static gantry supporting the top chuck assembly, an X-axis carriage drive supporting the bottom chuck assembly and an X-axis drive control configured to drive horizontally the X-axis carriage drive and the bottom chuck assembly from a loading zone to a process zone under the top chuck assembly and from the process zone back to the loading zone;

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loading a wafer pair comprising a carrier wafer bonded to a device wafer via an adhesive layer upon said bottom chuck assembly at the loading zone oriented so that an unbonded surface of the device wafer is in contact with the bottom assembly;

driving said X-axis carriage drive and said bottom chuck assembly to the process zone under the top chuck assembly;

placing an unbonded surface of the carrier wafer in contact with the top chuck assembly and holding said carrier wafer by said top chuck assembly;

heating said carrier wafer with a heater comprised in said top chuck assembly to a temperature around or above said adhesive layer's melting point;

initiating horizontal motion of said X-axis carriage drive along the X-axis by said X-axis drive control while heat is applied to said carrier wafer and while said carrier wafer is held by said top chuck assembly and said device wafer is held by said bottom chuck assembly and thereby causing the device wafer to separate and slide away from the carrier wafer; and

wherein said debonder further comprises a base plate supporting the X-axis carriage drive and the static gantry; and

wherein said base plate comprises a granite plate.

16. The method of claim **15**, wherein said bottom chuck assembly comprises a bottom chuck comprising a ceramic material and is designed to slide horizontally along the X-axis upon said X-axis carriage drive and to twist around the Z-axis.

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